

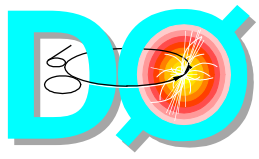
DØSMT

DØ Silicon Microstrip Tracker for run I a

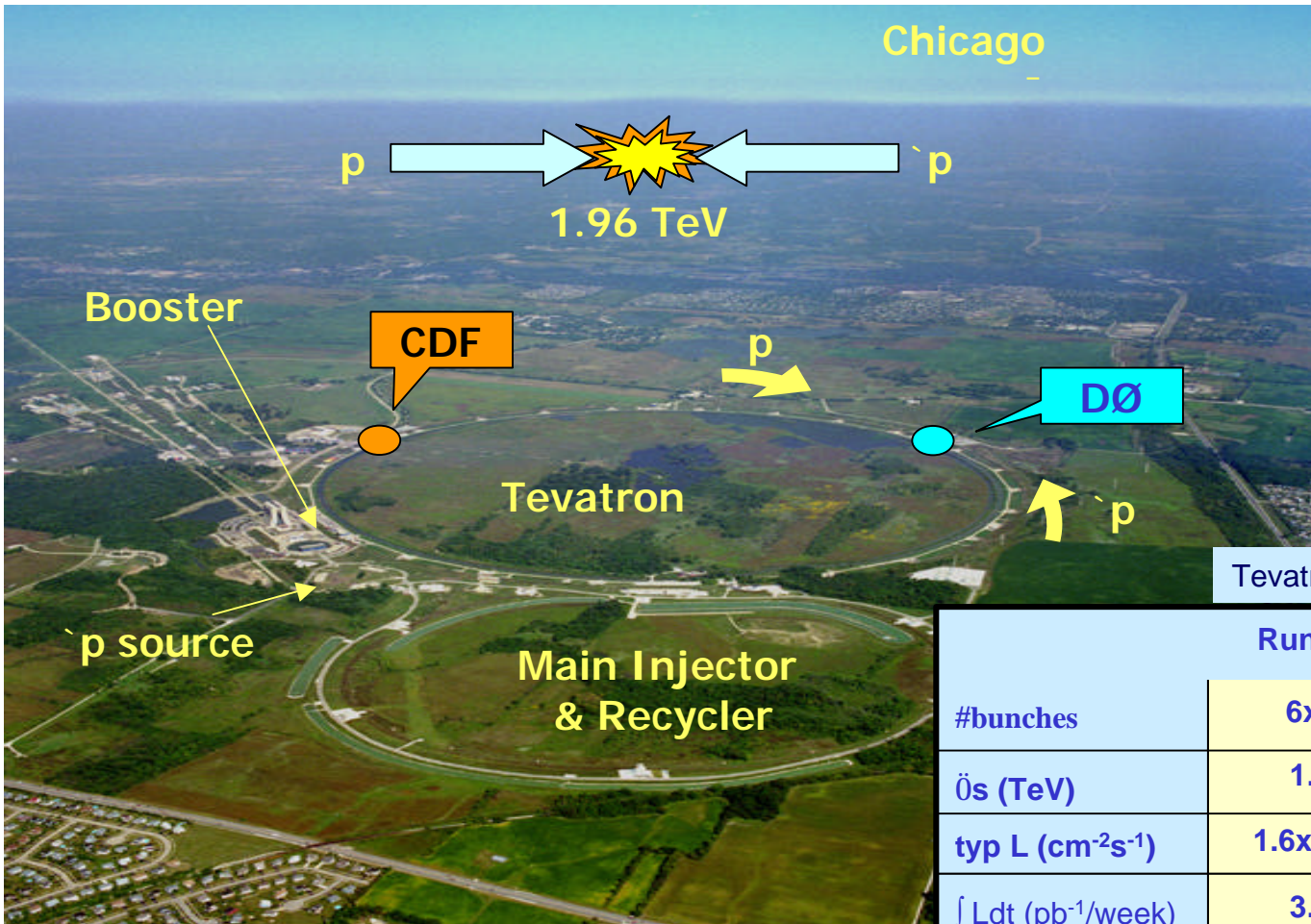
- Design
- Production
- Assembly
- Readout
- Installation
- Commissioning/Operation
- Some results

Eric Kajfasz (CPPMarseille)

Vertex2002 - Hawaii, November 4, 2002



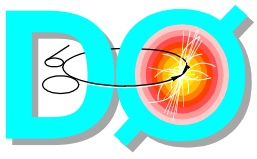
Fermilab Tevatron



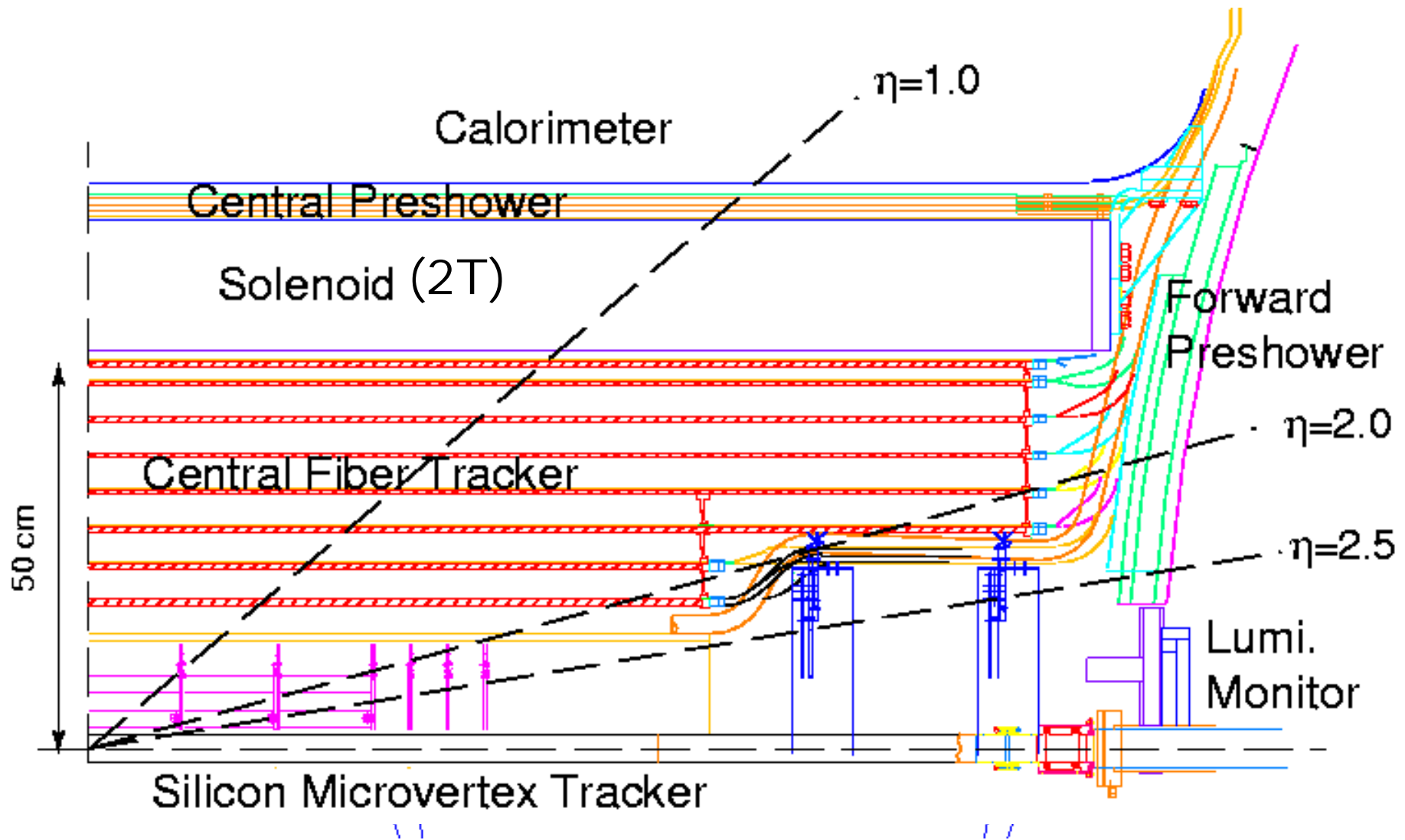
Run 1 → Run 2A → Run 2B
 $0.1 \text{ fb}^{-1} \rightarrow 2 \text{ fb}^{-1} \rightarrow 15 \text{ fb}^{-1}$

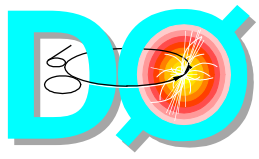
	Run 1B	Run 2A	Run 2B
#bunches	6x6	36x36	140x103
ös (TeV)	1.8	1.96	1.96
typ L ($\text{cm}^{-2}\text{s}^{-1}$)	1.6×10^{30}	8.6×10^{31}	5.2×10^{32}
∫ Ldt ($\text{pb}^{-1}/\text{week}$)	3.2	17.3	105
bunch xing (ns)	3500	396	132
interactions/xing	2.5	2.3	4.8





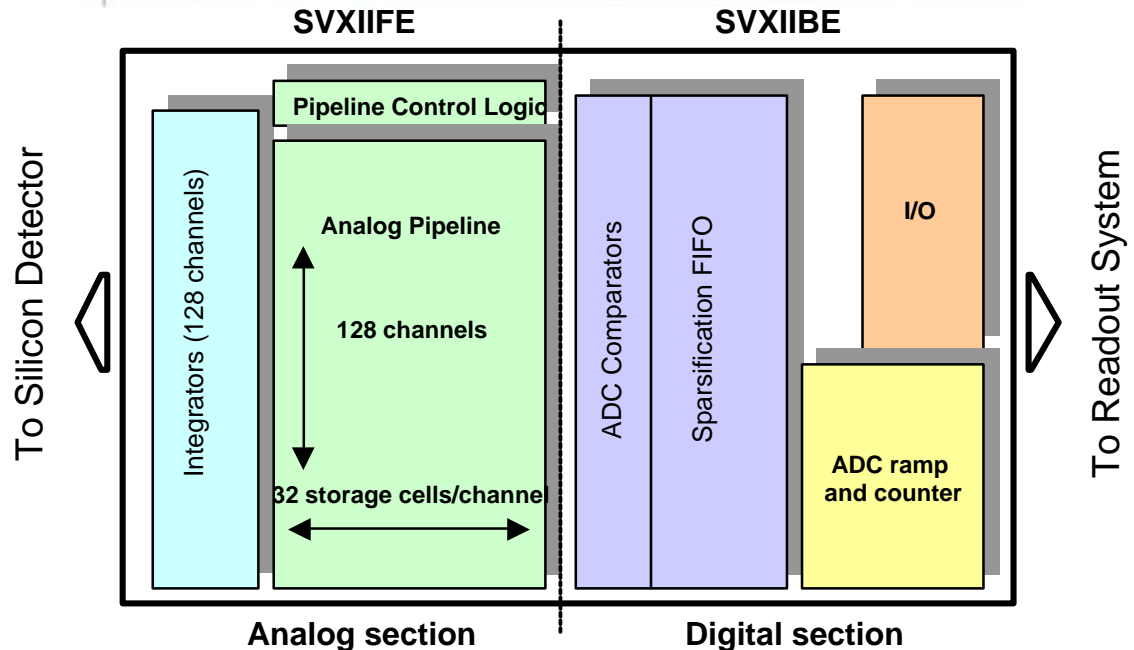
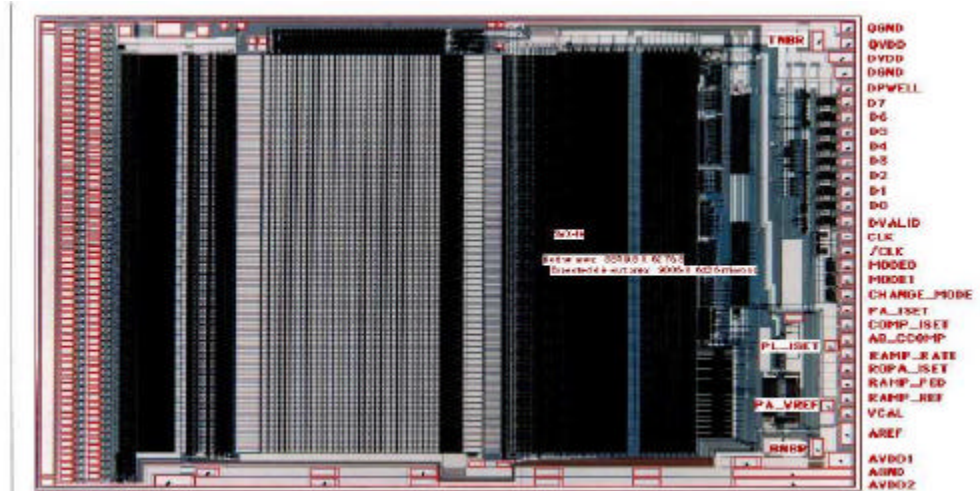
Run I I a SMT Design

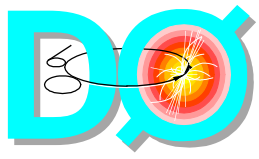




SVXIIe chip

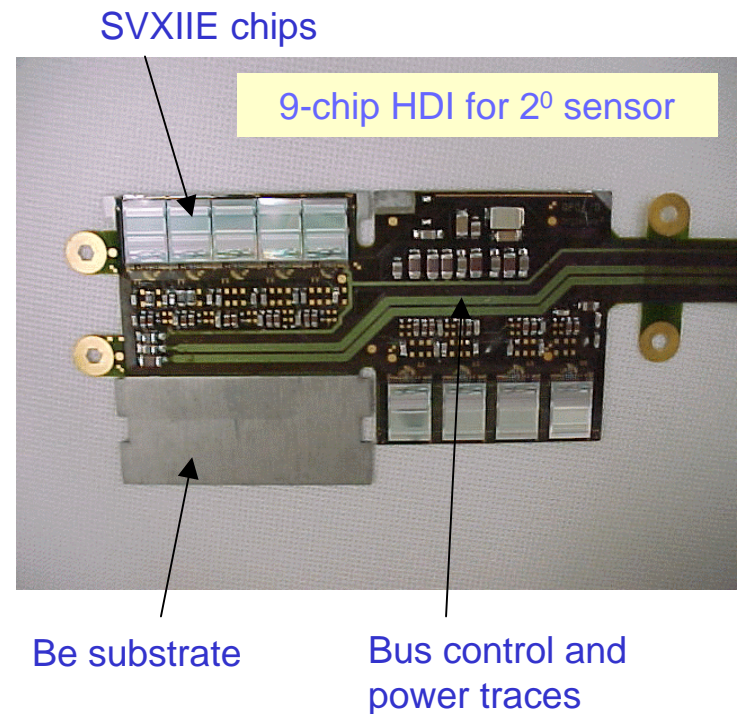
- 1.2 μm CMOS amplifier/analog delay/ADC chip fabricated in the UTM C rad hard process
- Designed by LBL/FNAL
- Some features:
 - 128 channels
 - 32 cell pipeline/channel
 - 8-bit Wilkinson ADCs
 - Sparsification
 - 53 MHz readout
 - 106 MHz digitization
 - $6.4 \times 9.7 \text{ mm}^2$
 - ~ 85,000 transistors
 - noise: $490e + 50e/pF$

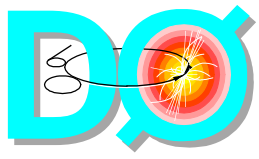




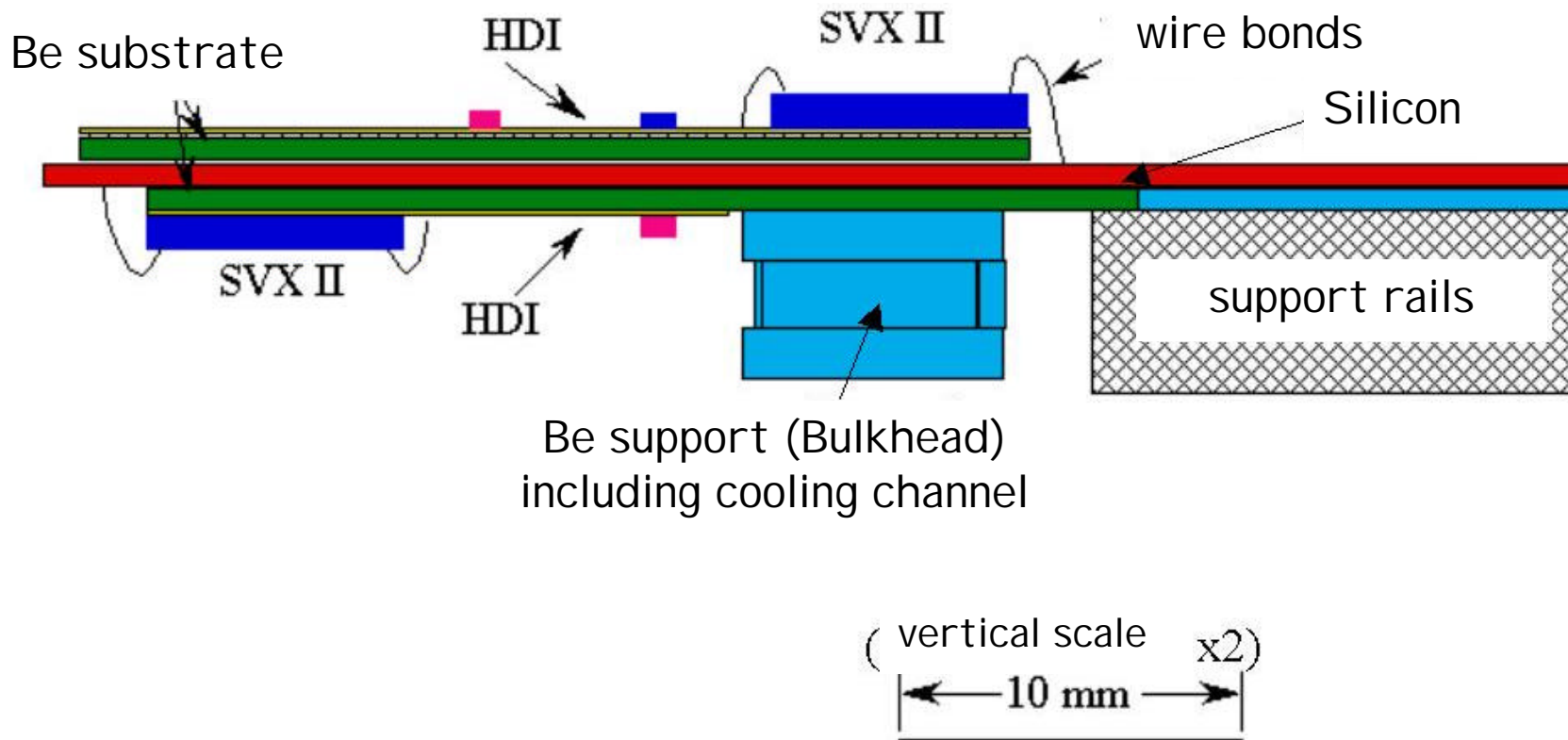
High Density Interconnect

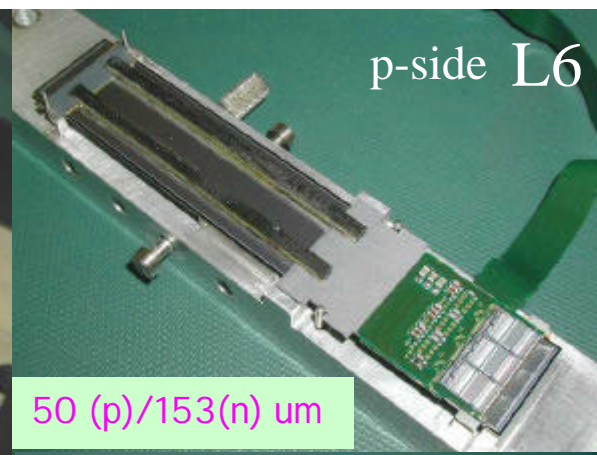
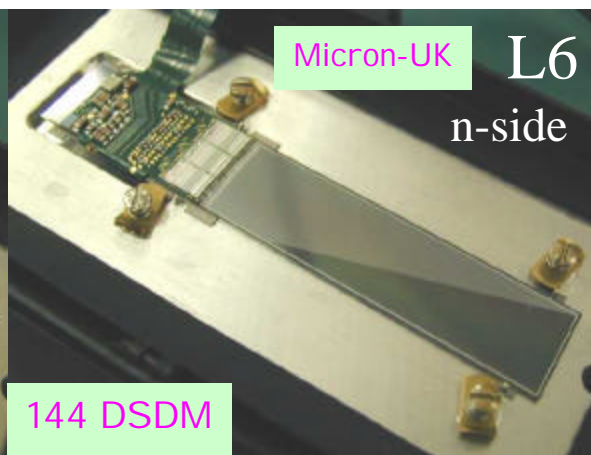
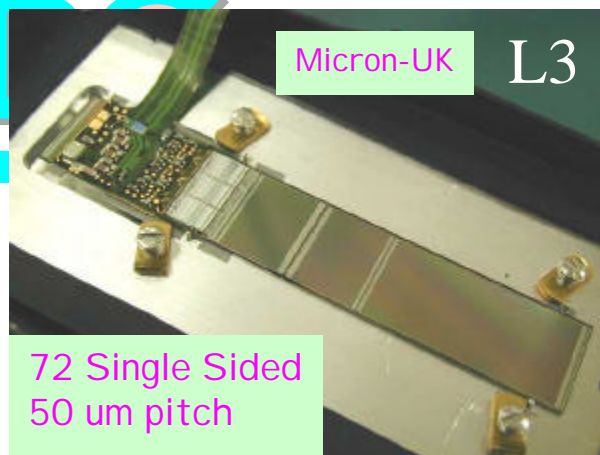
- Kapton based flex circuits with 0.2 mm pitch for chip mounting
- Laminated to Beryllium substrate and glued to Silicon sensor
- Connects Sensor to SVXII chips and SVXII chips to flex circuit via wire bonds (Al wedge bonding)
- Connects to a Low Mass Cable which carries the signals out of the interaction region



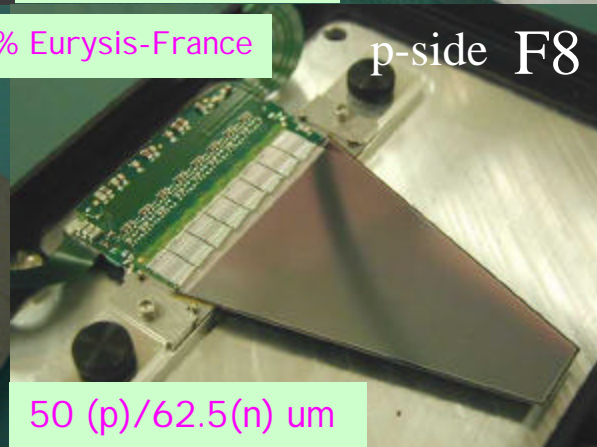
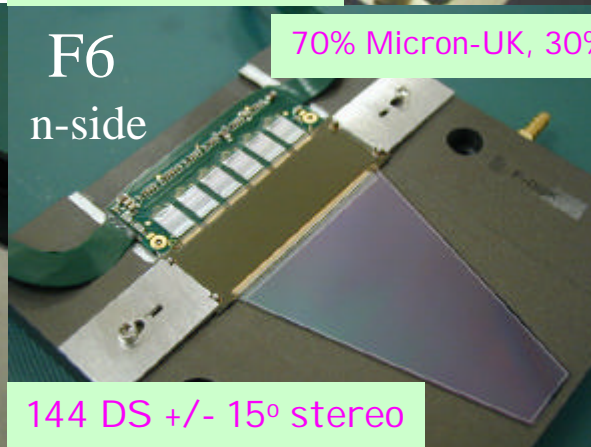
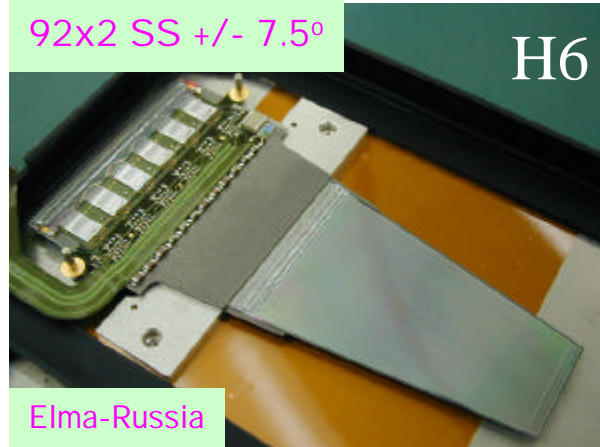
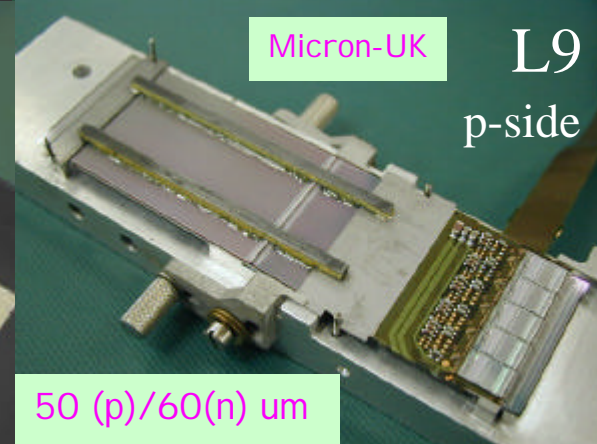
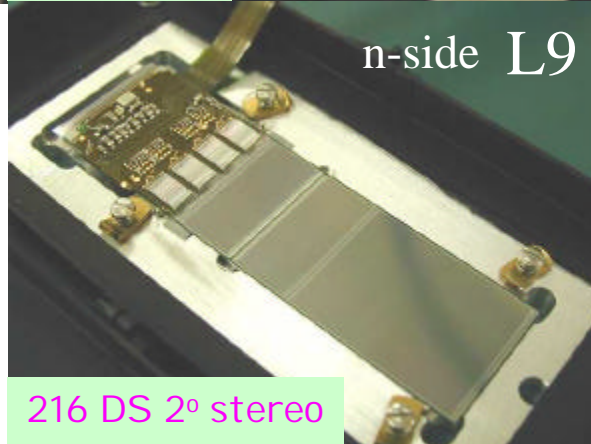


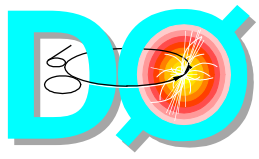
Production: ladder design



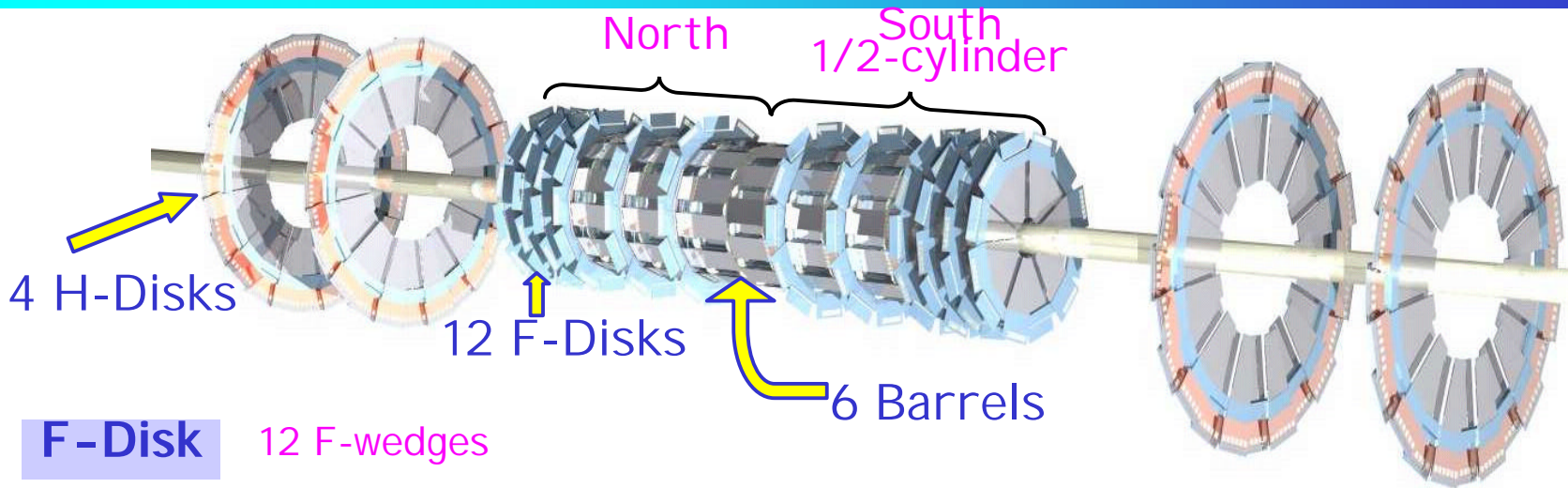


Family of DOSMT
Detector types
(all AC coupled)





Run I I a SMT Design



F-Disk

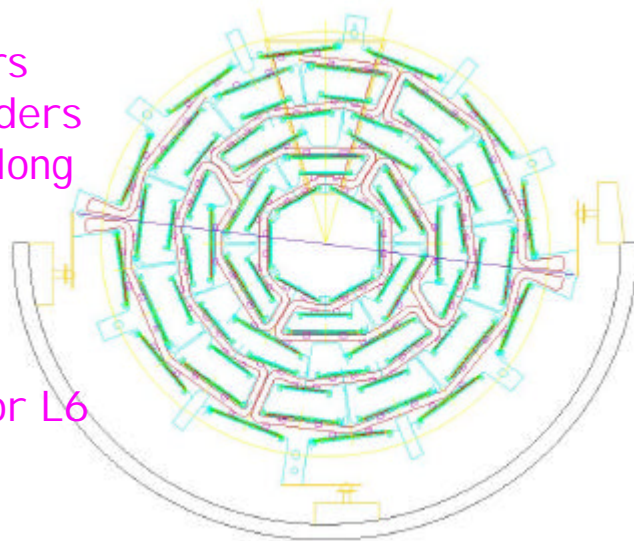
12 F-wedges

H-Disk

24 H-wedges

Barrel

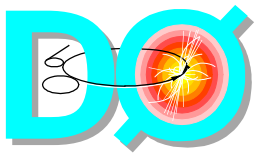
8 layers
72 ladders
12 cm long



Layers 1,2,5,6: L3 or L6
Layers 3,4,7,8: L9

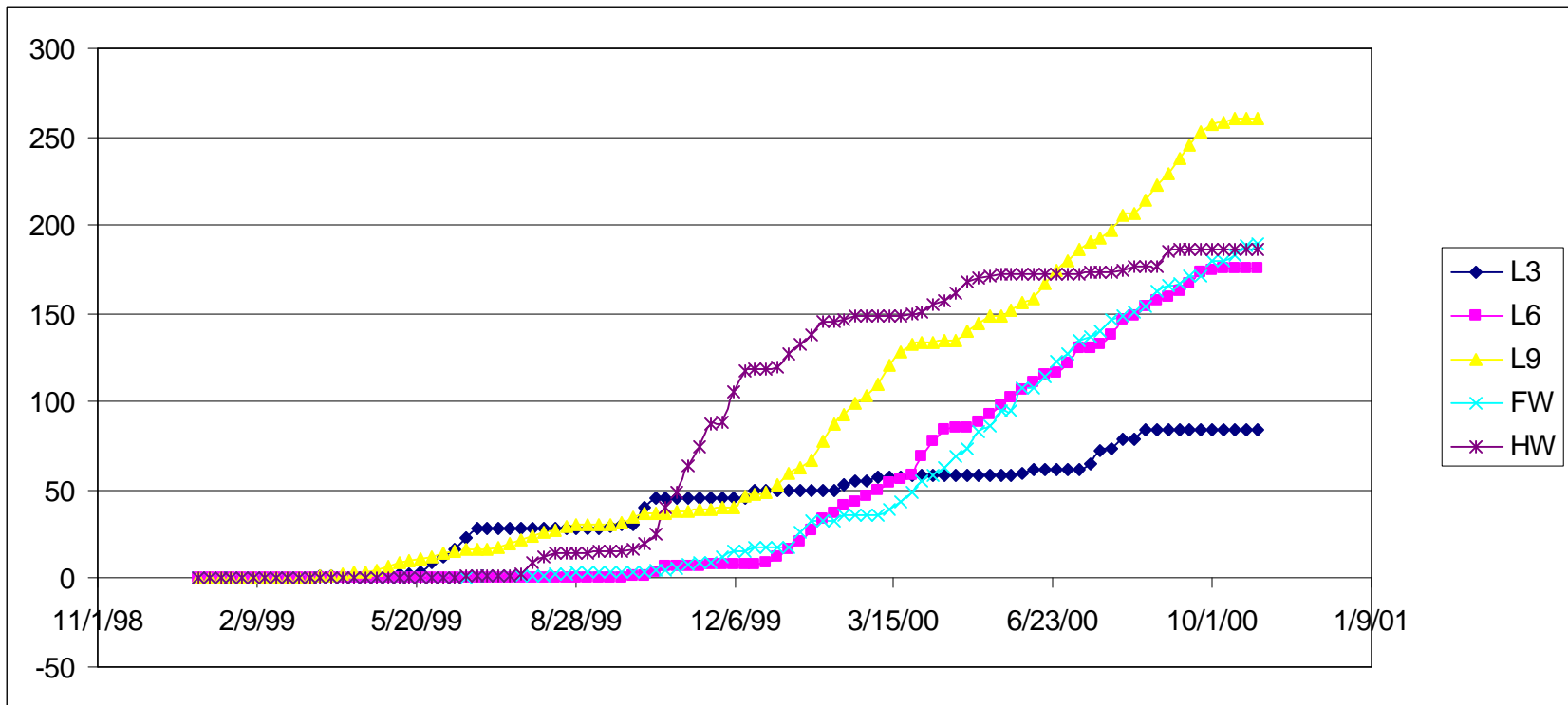
	Barrels	F-Disks	H-Disks
Channels	387072	258048	147456
Modules	432	144	96
Si Area	1.3 m ²	0.4 m ²	1.3 m ²
Inner R	2.7 cm	2.6 cm	9.5 cm
Outer R	9.4 cm	10.5 cm	26 cm

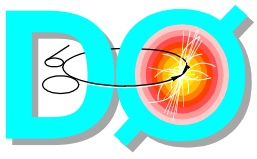
6192 R/O chips = 792,576 channels
> 1.5 million wire bonds



Production: Rates

Production mainly paced by problems with HDIs and Silicon sensors
(yields, delivery delays ...)

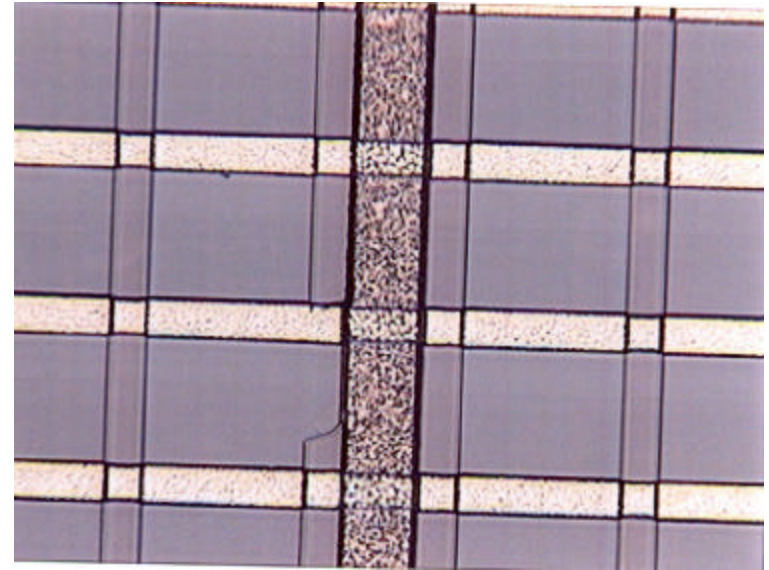




Production: Sensor problems

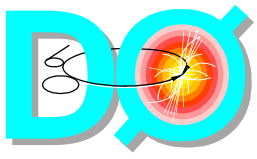
● Sensor lithography defects

- A silicon manufacturing problem produced p-stop isolation defects in the 90° stereo ladders. This resulted in a 30% yield from the manufacturer.

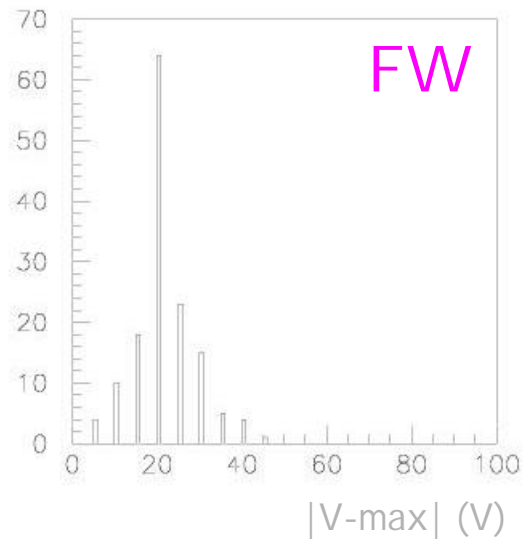
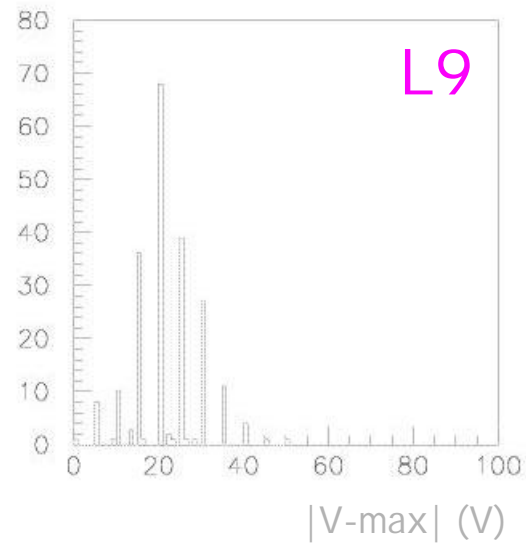
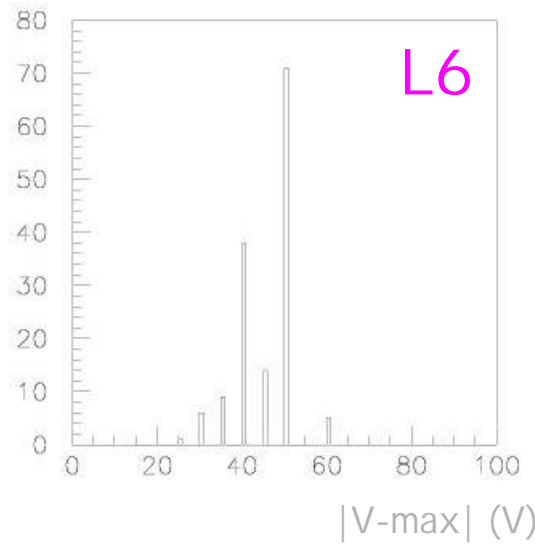


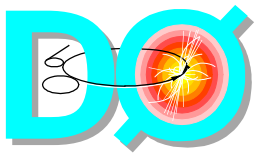
● Micro-discharge effect

- With negative p-side bias on double-sided detectors, we observed micro-discharges producing large leakage currents and noise above a certain breakdown voltage.
- The effect occurs along the edges of the p implants, where large field distortions and charge accumulations result from misalignment of electrodes with implants.

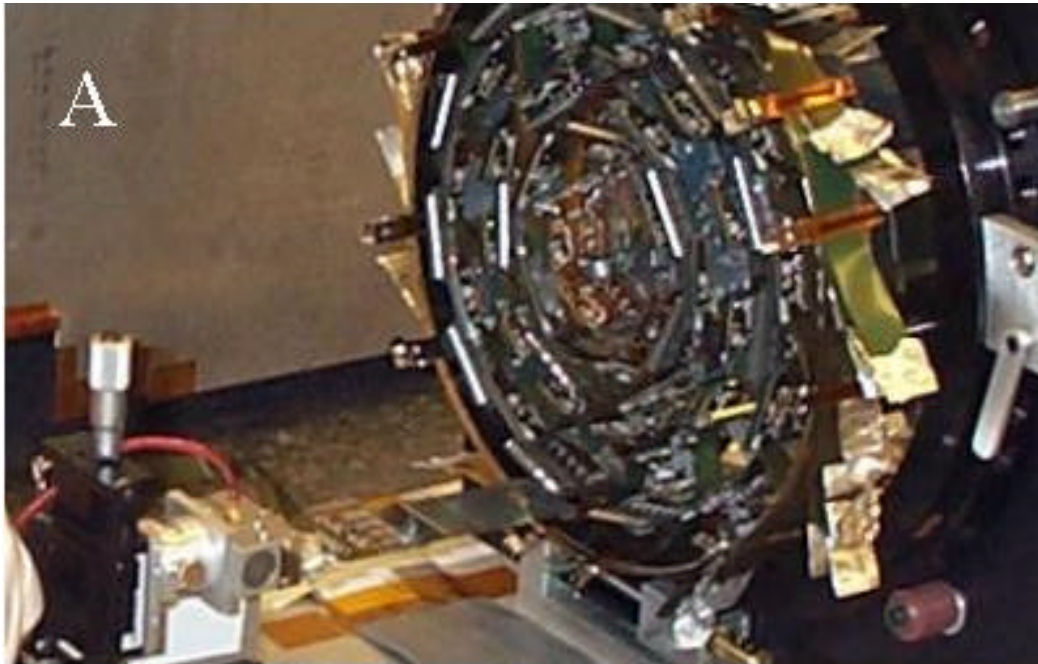


Production: V-max



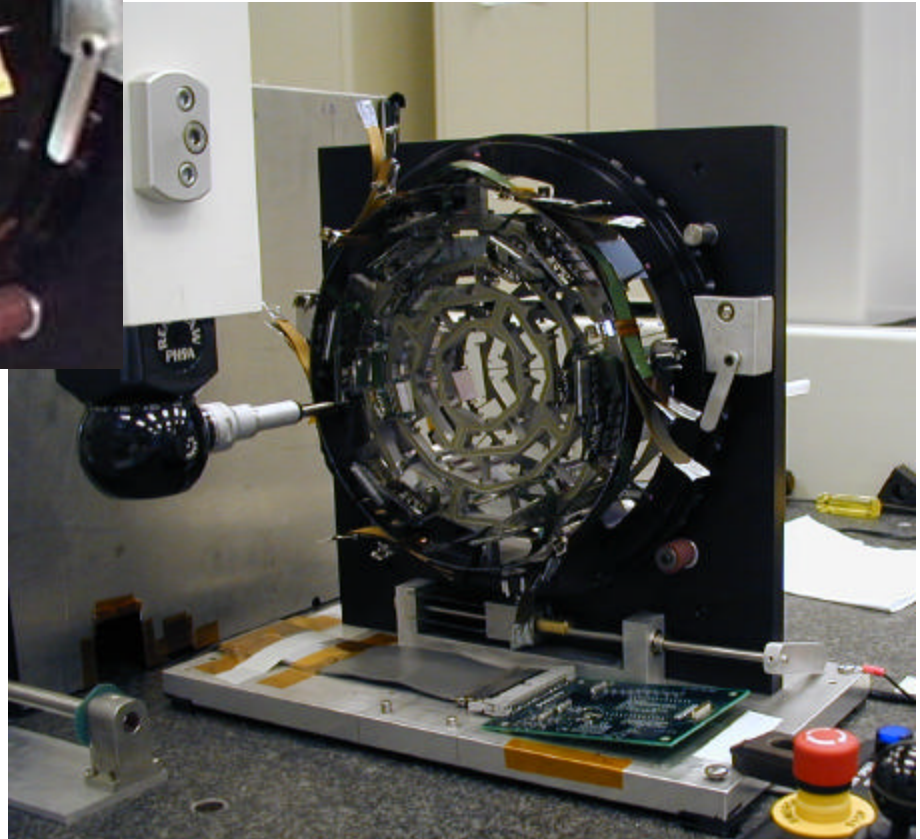


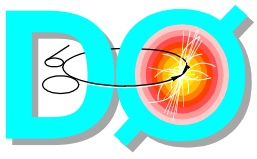
Assembly: Barrel assembly



- Ladders placed on barrels using an insertion fixture

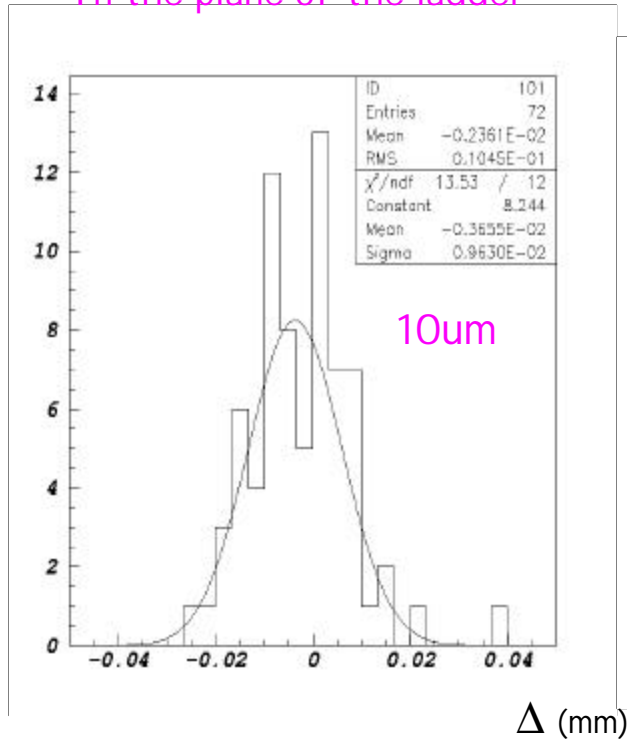
- Internal alignment done using a CMM (touch probe)



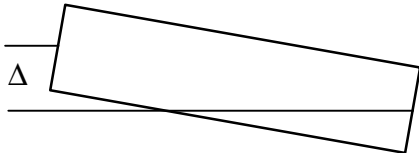


Assembly: Barrel 2 alignment

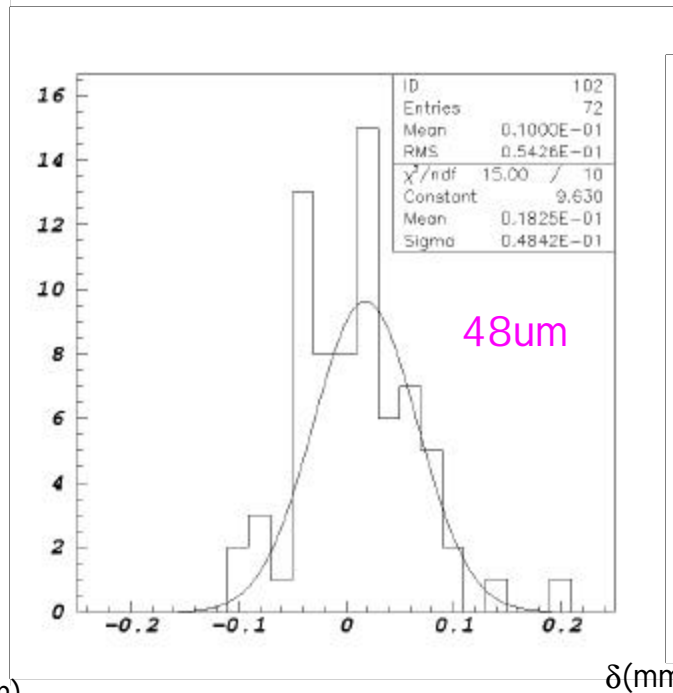
In the plane of the ladder



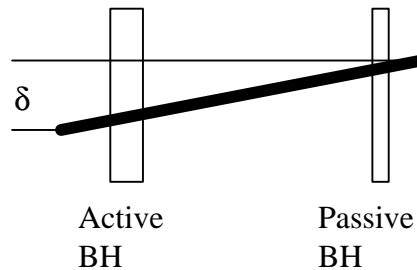
$s(D) = 10\mu\text{m}$ induces a 3um error



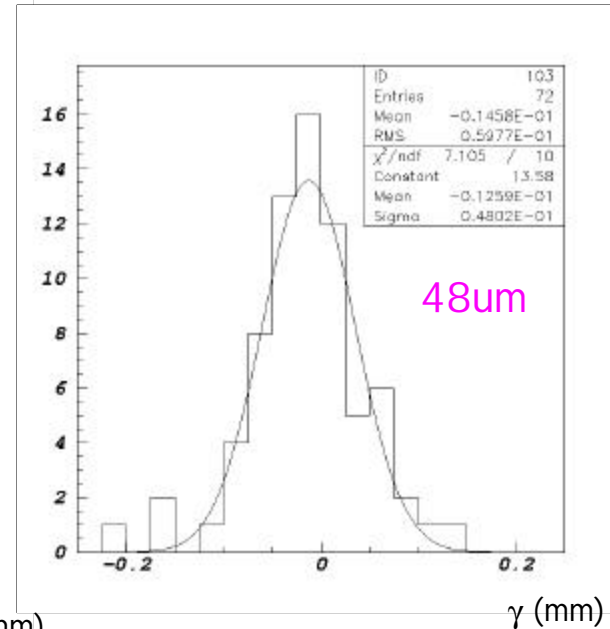
Around ladder short axis



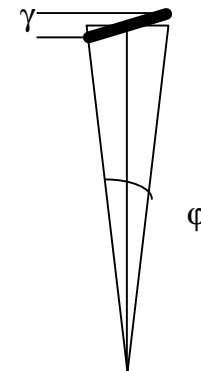
$s(d) = 48\mu\text{m}$ induces a 3um error

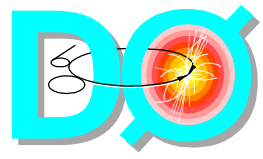


Around ladder long axis

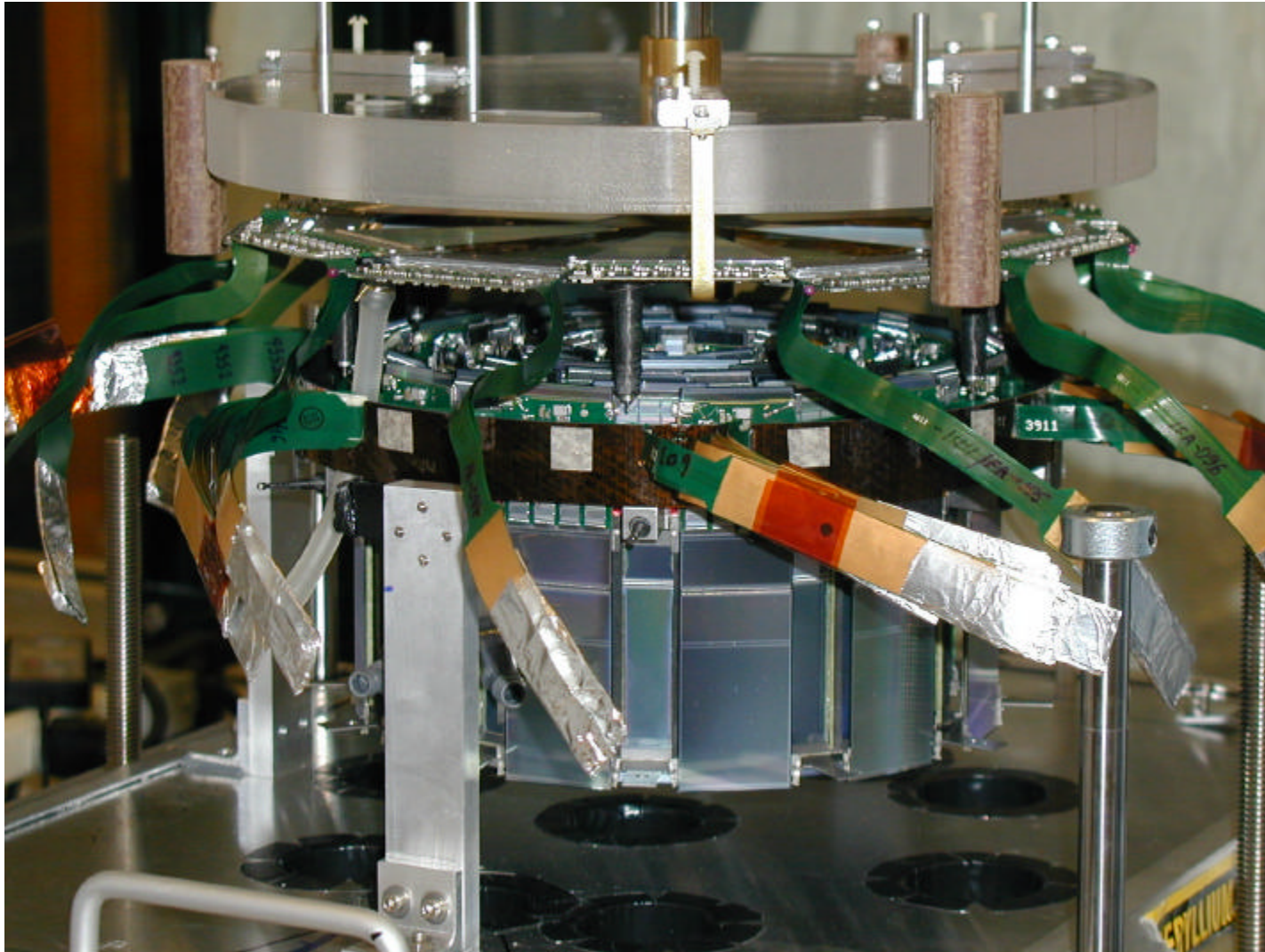


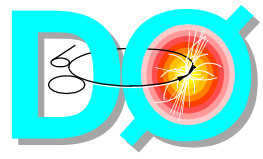
$s(g) = 48\mu\text{m}$ induces a 2um error



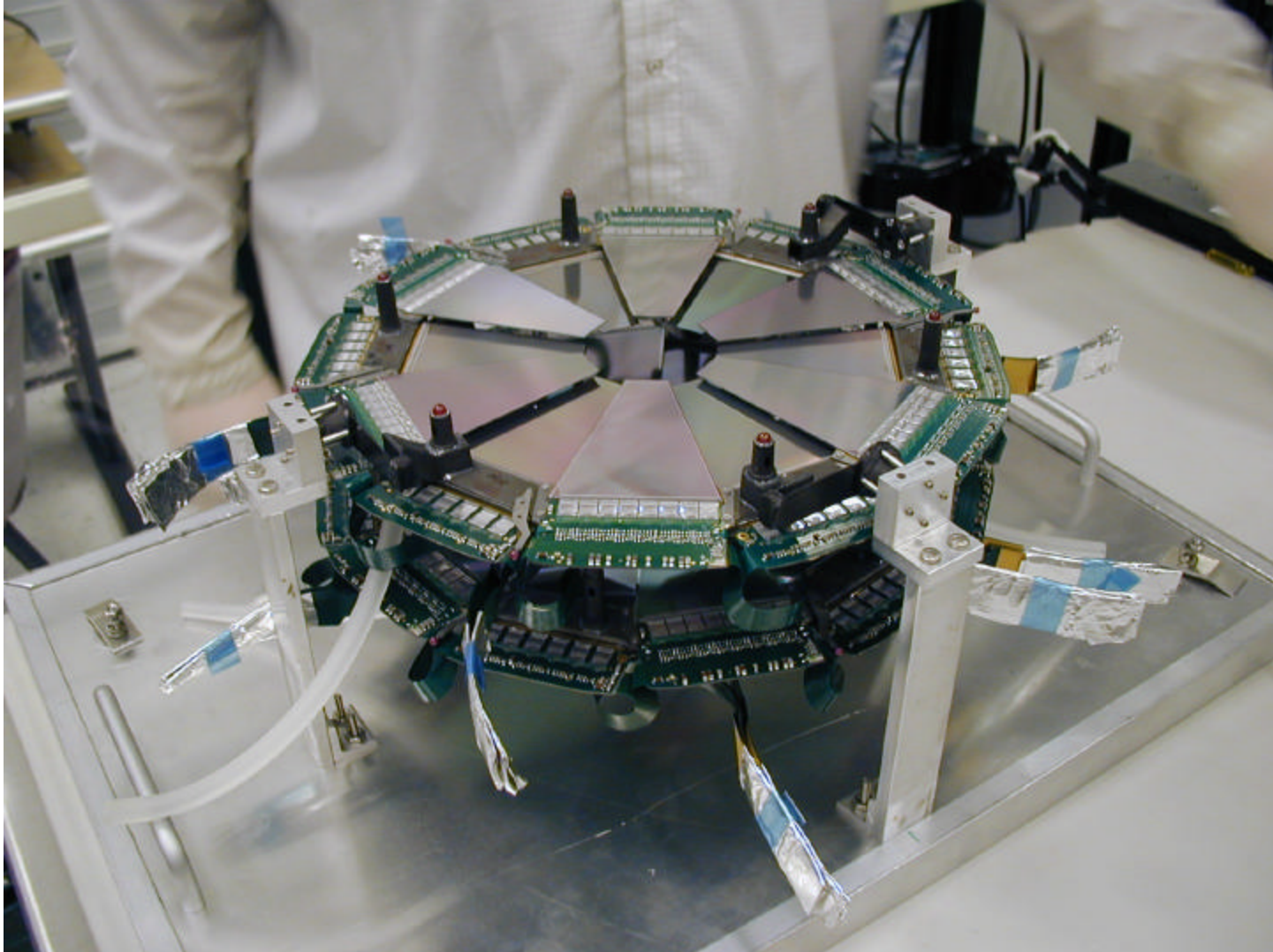


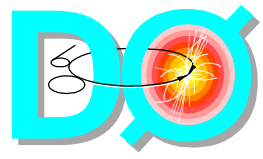
Assembly: Barrel-Fdisk mating



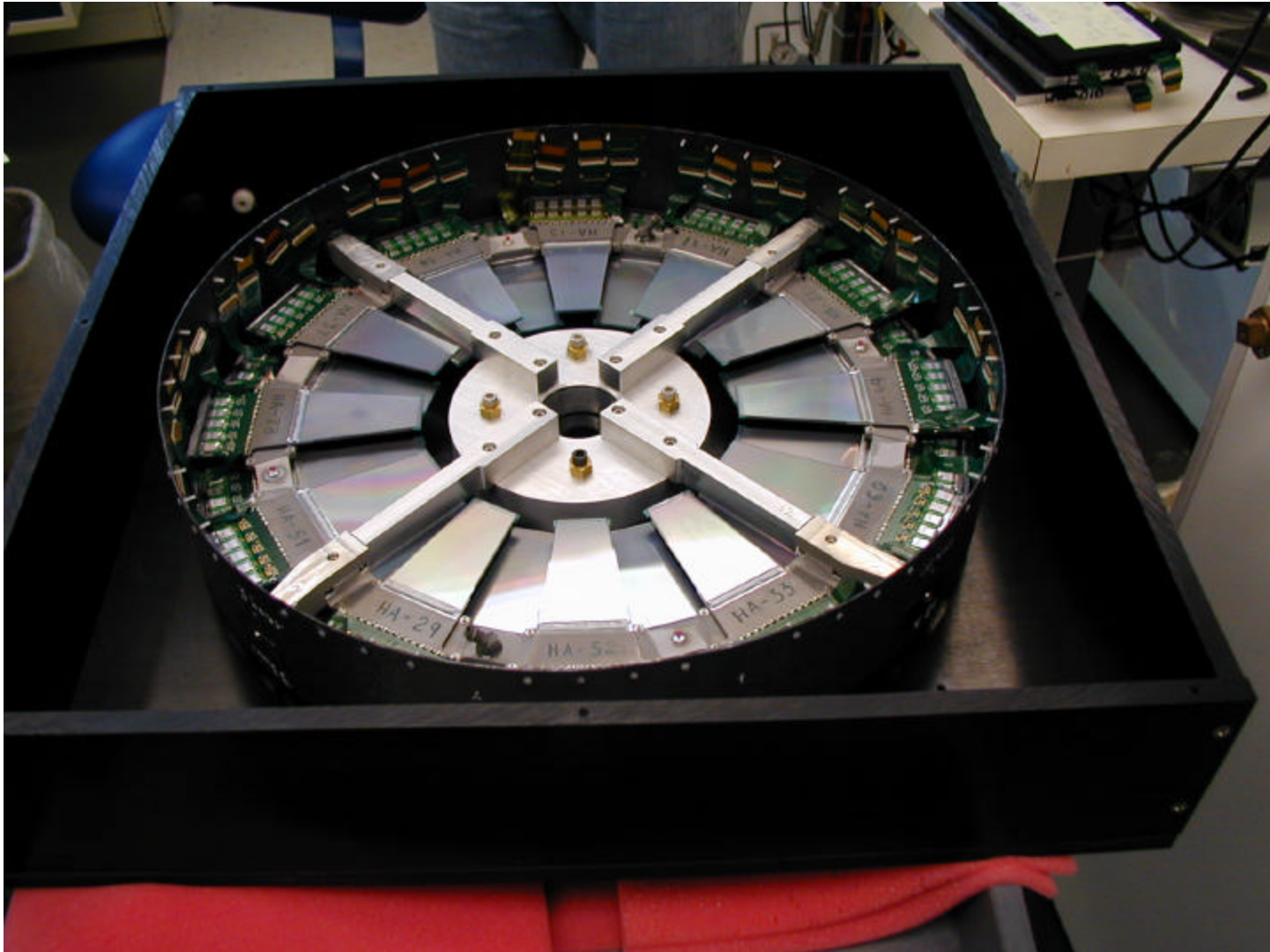


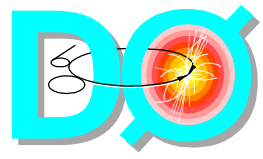
Assembly: End Fdisks mating



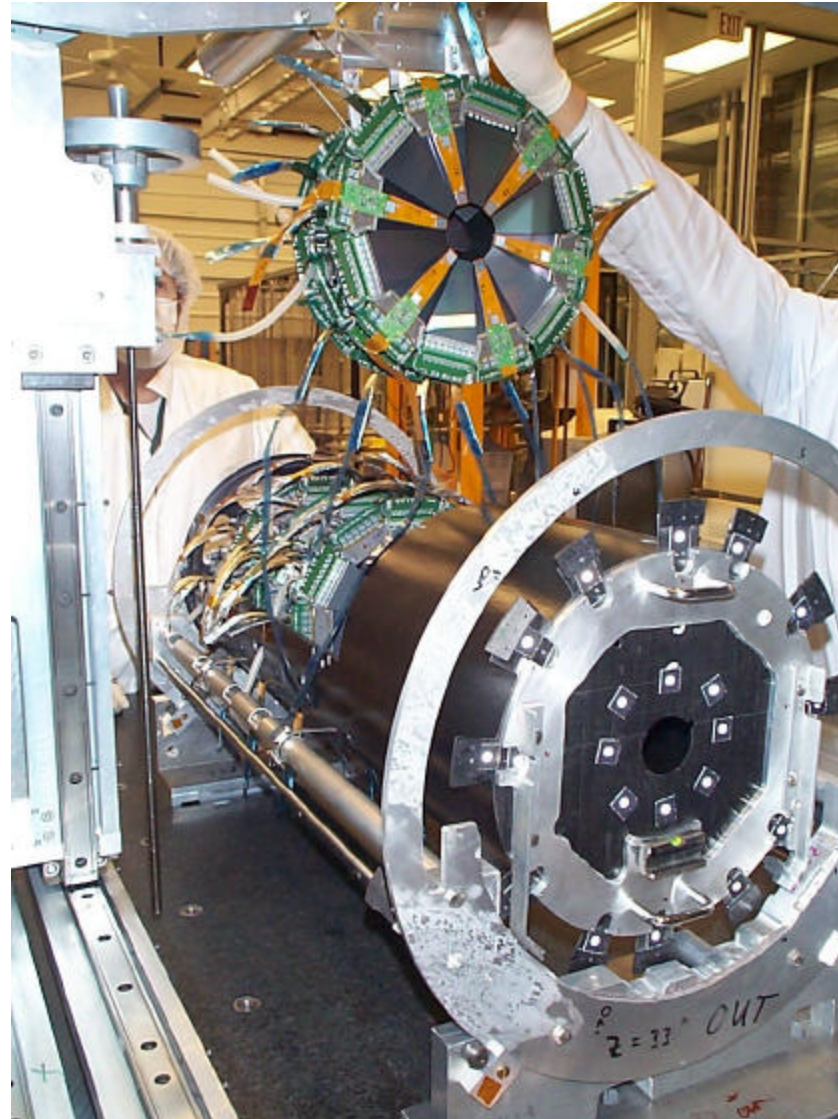


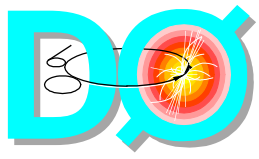
Assembly: Hdisk



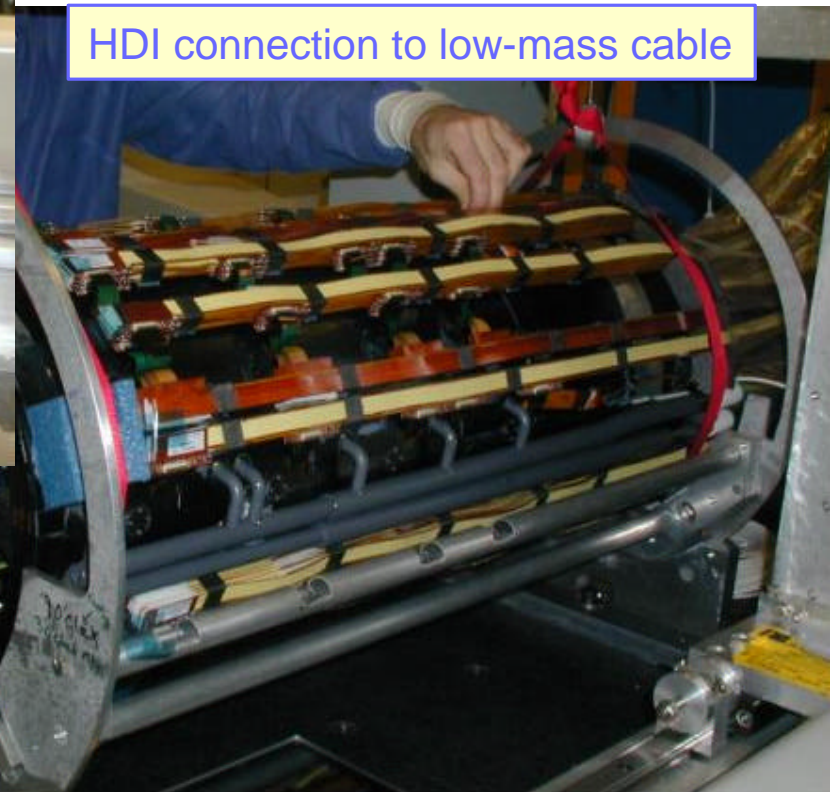
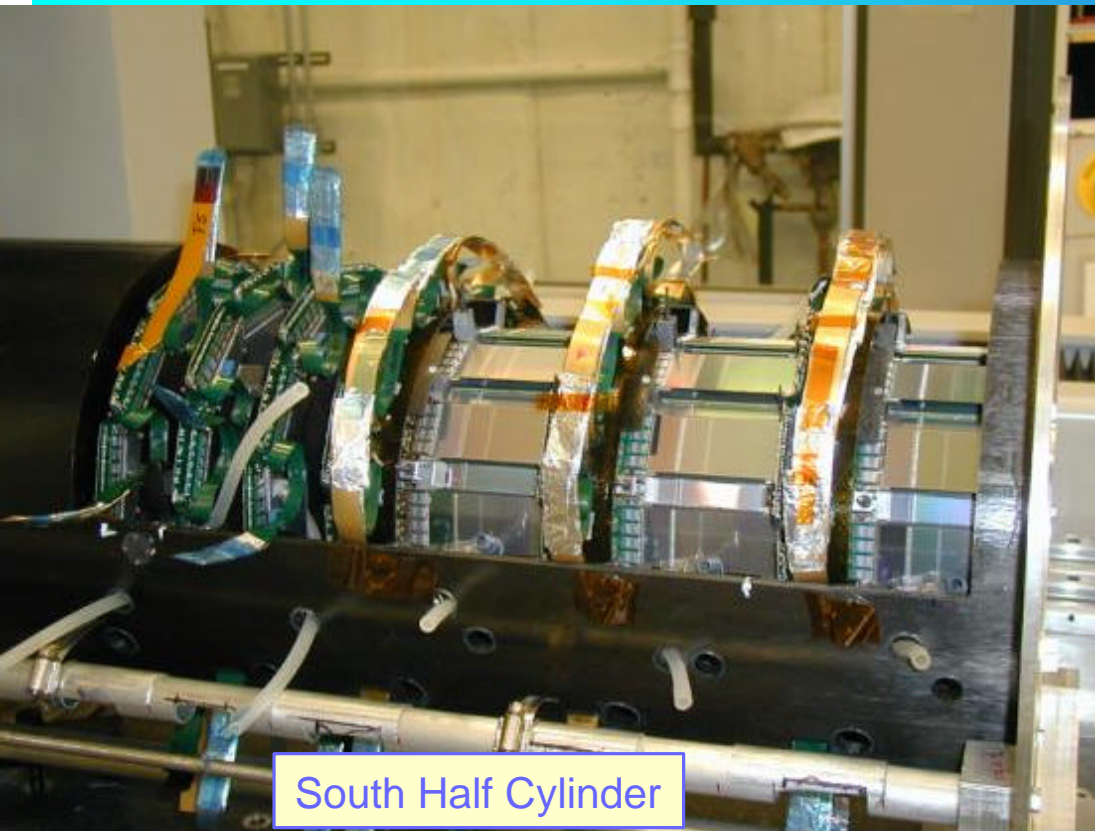


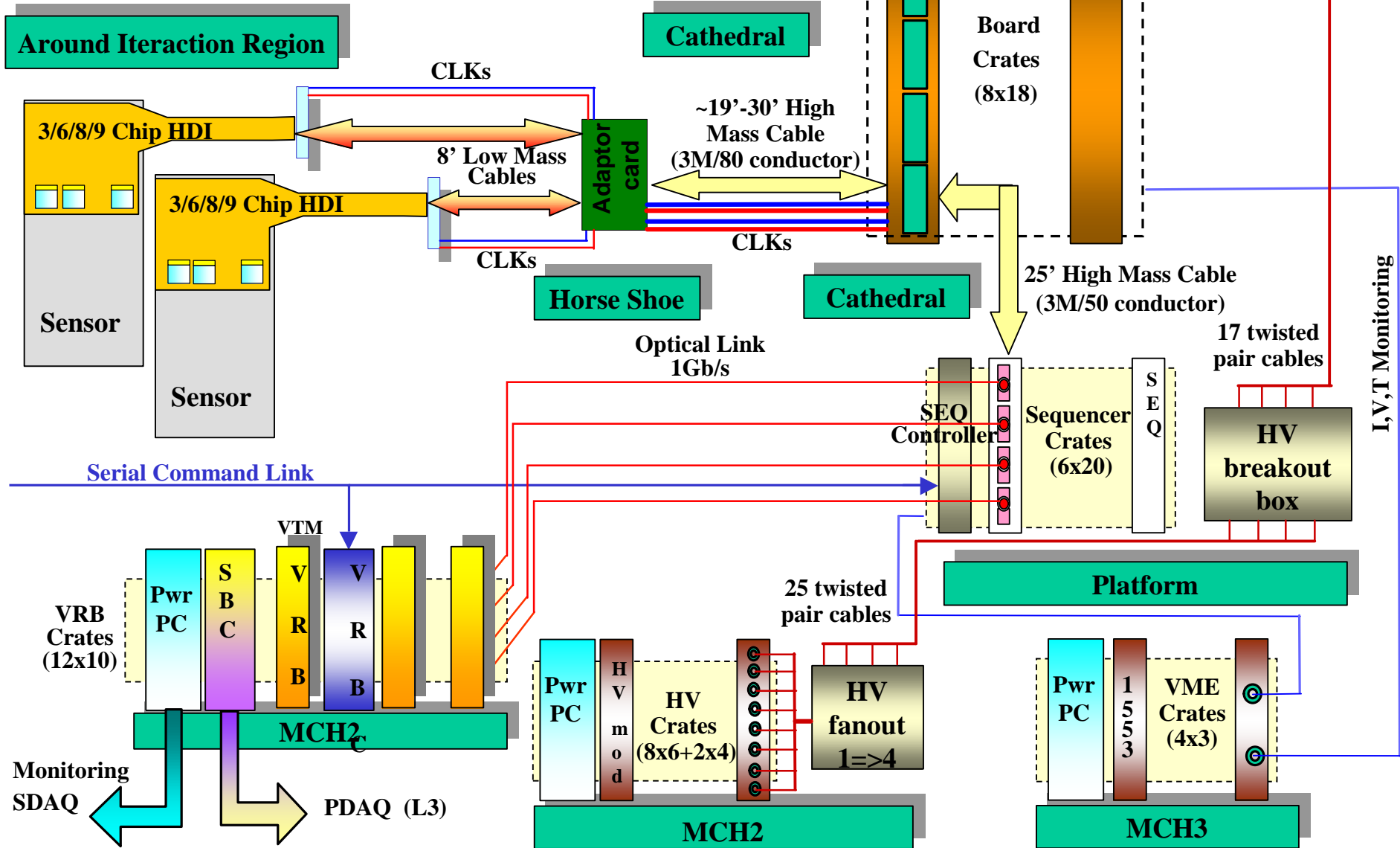
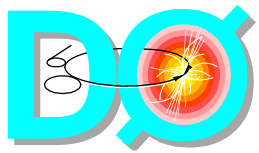
Assembly: Radiation monitors



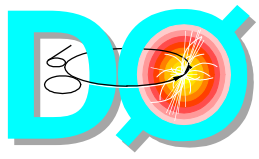


Assembly: 1/2-cylinder





PowerPCs and Single Board Computers are accessed thru Ethernet



Readout Electronics

Interface Boards

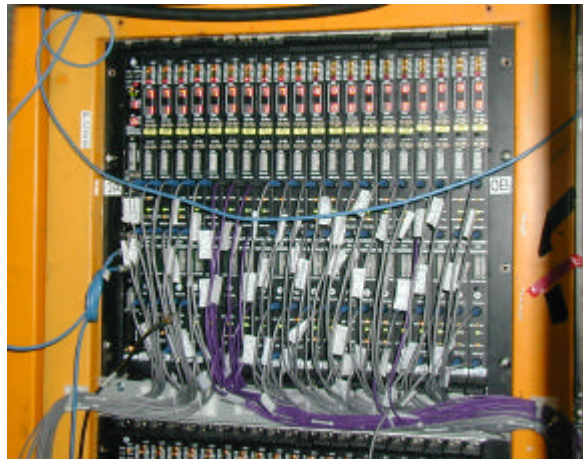
- 8 crates (144 boards) located inside the detector volume
- Regenerates signals
- SVX monitoring and power management
- Bias voltage distribution

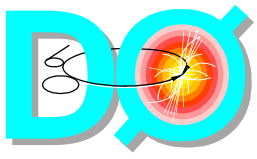
SEQuencers

- 6 crates (120 boards) located on the detector platform
- Use SVX control lines to actuate acquisition, digitization and readout
- Convert SVX data to optical signals

VRBs (Readout Buffers)

- 12 crates (120 boards) located in counting house
- Data buffer pending L2 trigger decision
- Input @ 5-10 kHz L1 accept rate ~ 50 Mb/s/channel
- Output @ 1 kHz L2 accept rate ~ 50 Mb/s

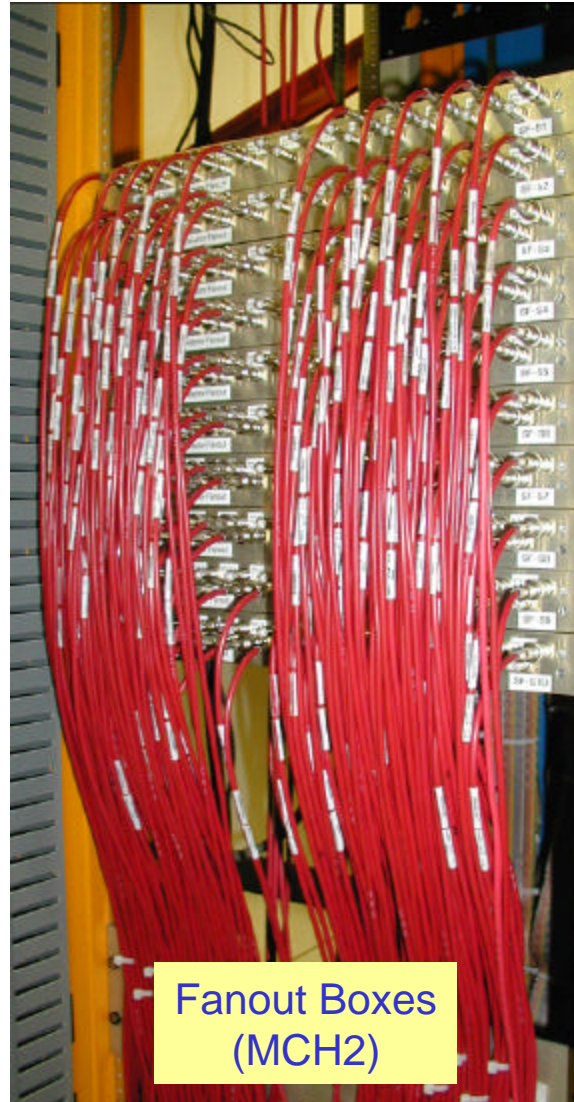




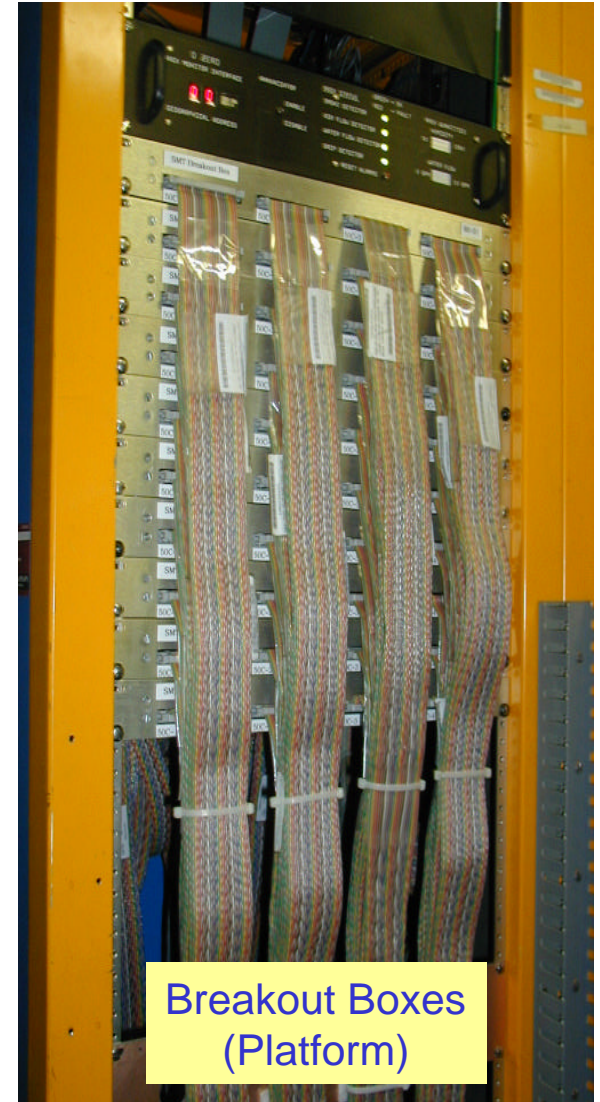
HV distribution



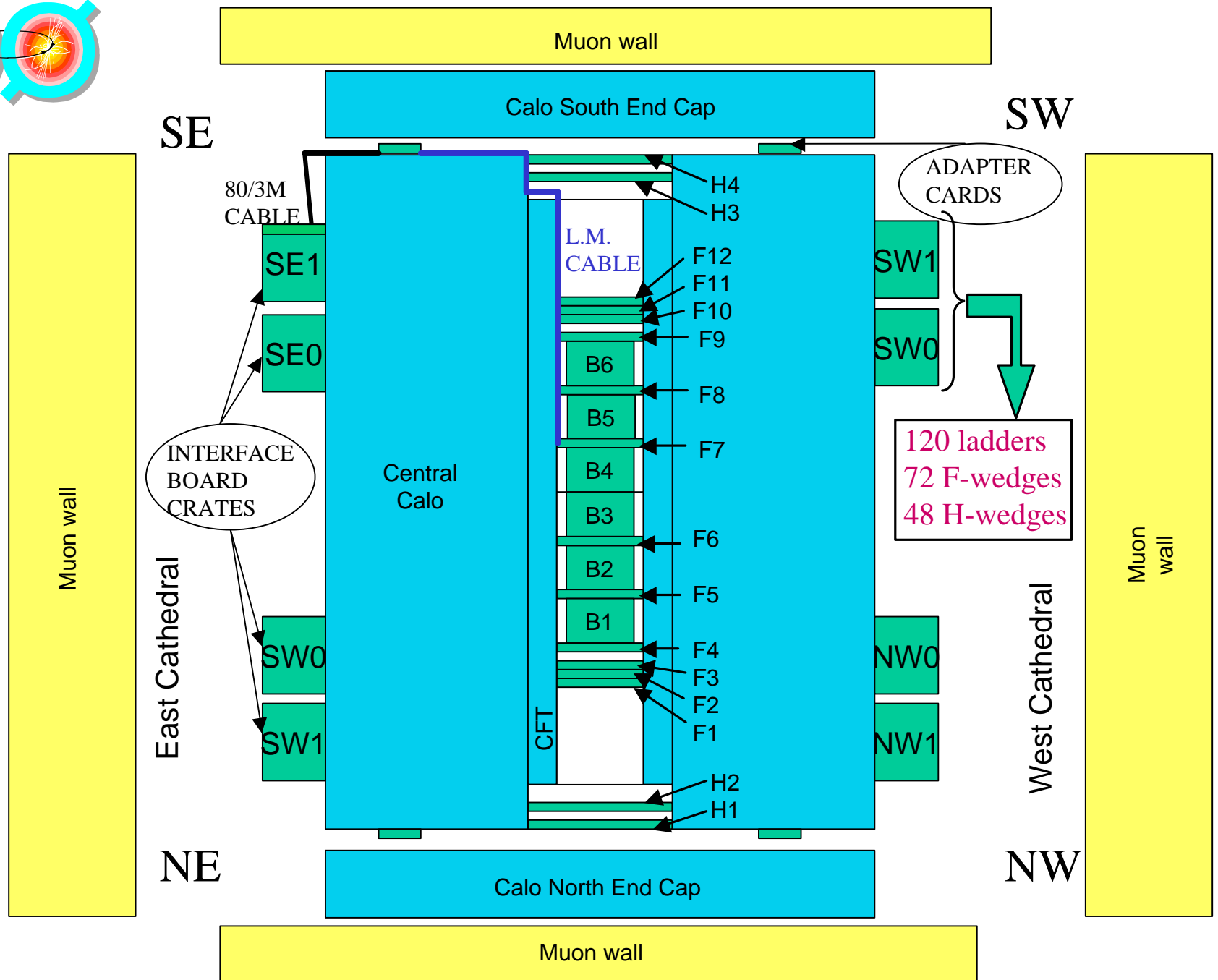
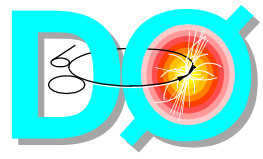
HV Modules
(MCH2)

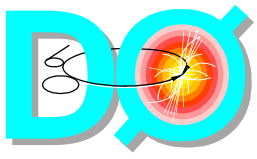


Fanout Boxes
(MCH2)



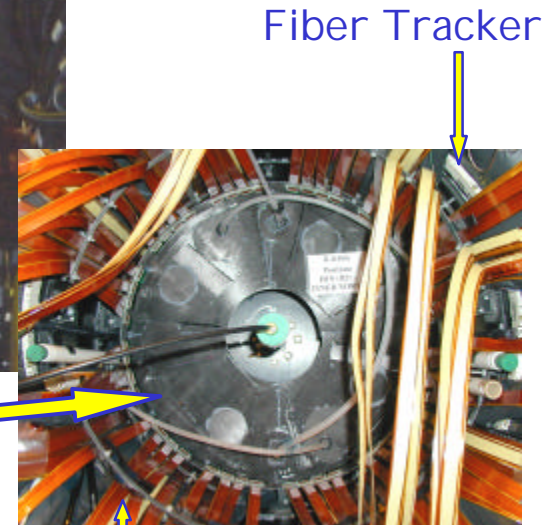
Breakout Boxes
(Platform)





Installation

- Cylinder installation was completed on 12/20/00
 - A 1/2-cylinder of 3 barrels and 6 F disks was inserted into each end of the CFT bore
- H Disk installation was completed on 2/6/01
- The cabling (~15,000 connections) and electronics installation was completed in May 2001



Fiber Tracker

Calorimeter

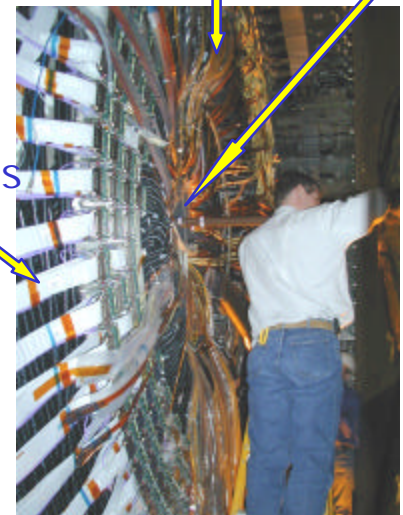


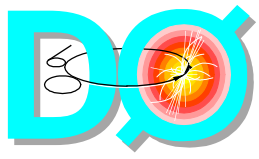
Interface Boards

Low Mass Cables

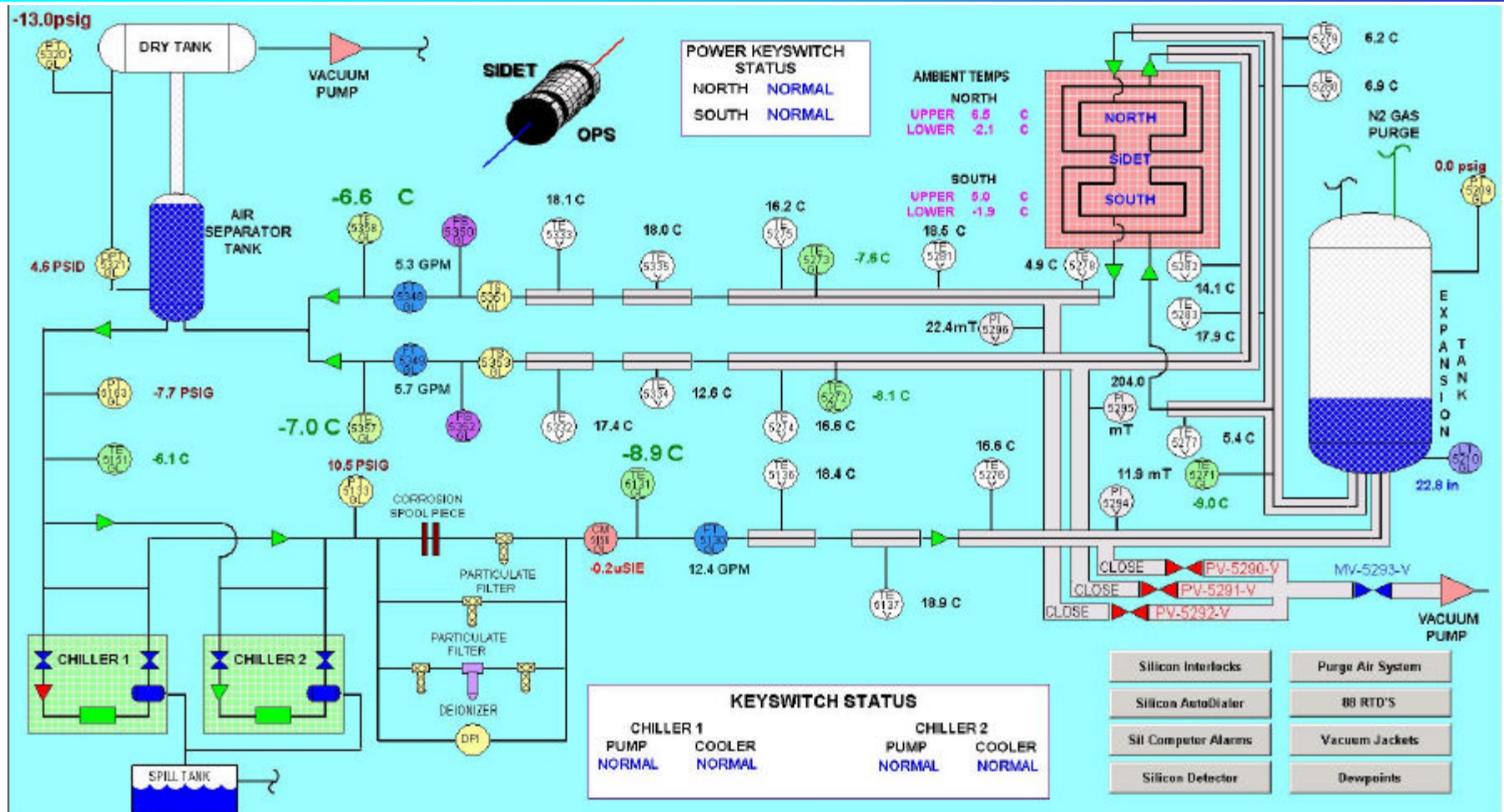
SMT

High Mass Cables

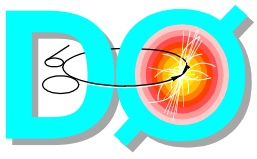




Installation: Cooling system

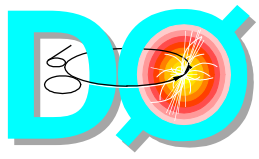


- 30% glycol + water at -10°C (\Rightarrow detectors between -5 and 0°C)
- The tracking volume is purged with dry air to prevent condensation



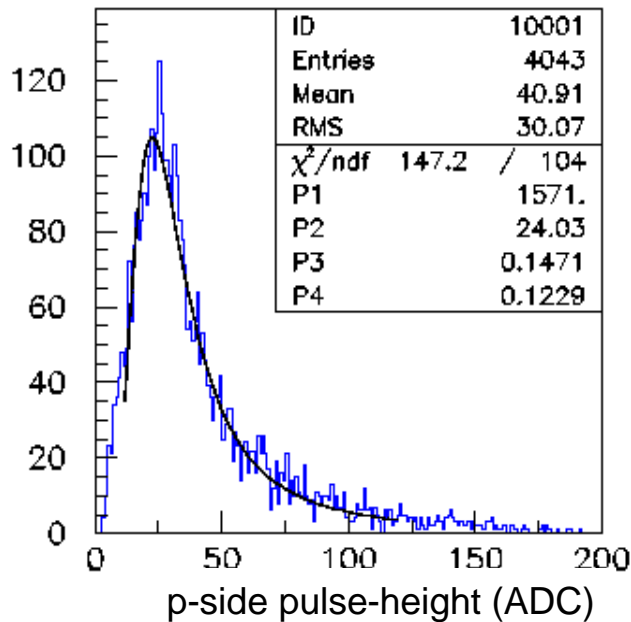
Commissioning: Status

- entire detector is connected and powered
- currently collecting essentially physics data. Calibration and commissioning data when no beam present
- some problems we run into:
 - had failure of some IB LV PS. Fixed and reliable now.
 - IB crate heat exchangers water leak
=> had to disconnect 2 out of 8
 - Hygroscopicity and not-too-professional assembly of some HV fan out boxes leading to bias current instabilities => tried to fix them but designed and ordered new ones
 - Failure of a few detectors since the last shutdown
=> not necessarily an HDI problem. Part of them will be fixed in January 2003. Fraction of enabled detectors:
 - on 12/01/01: 93% (Barrels) - 95% (F-Disks) - 90% (H-Disks)
 - on 09/31/02: 89% (Barrels) - 94% (F-Disks) - 84% (H-Disks)



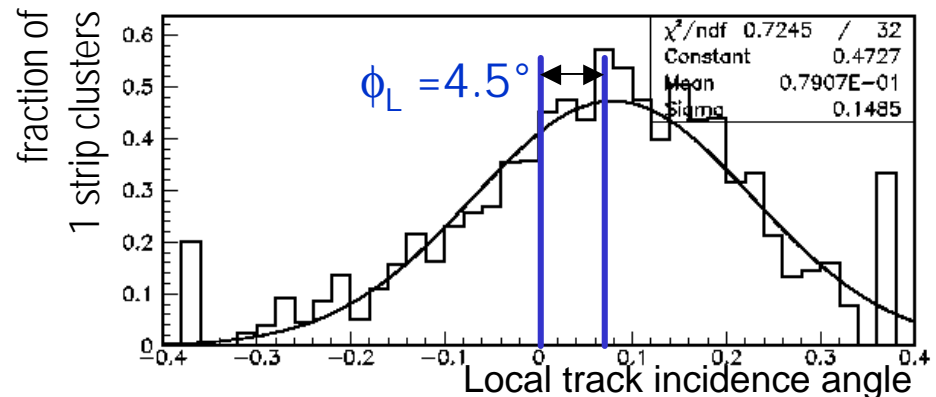
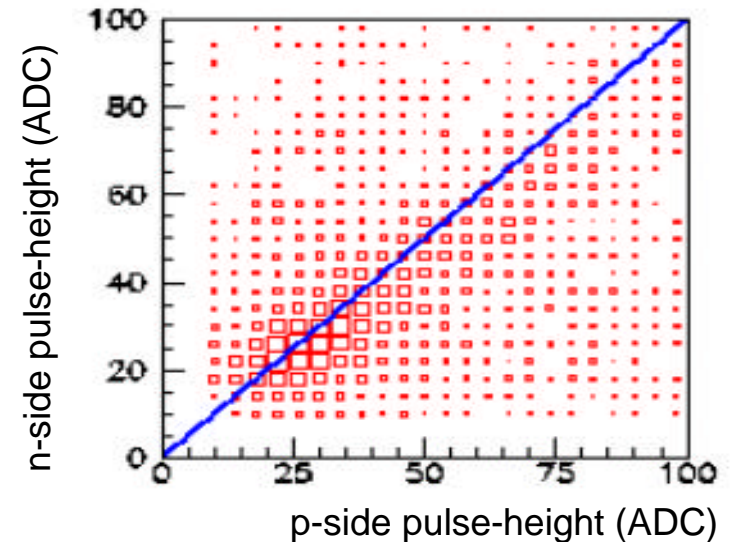
Commissioning: Charge collection

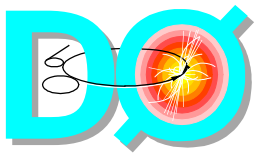
- Cluster charge (corrected for track angle): 1 mip ~ 25 ADC counts. Noise < 2ADC counts.



- Lorentz angle: The charge deflection due to the magnetic field

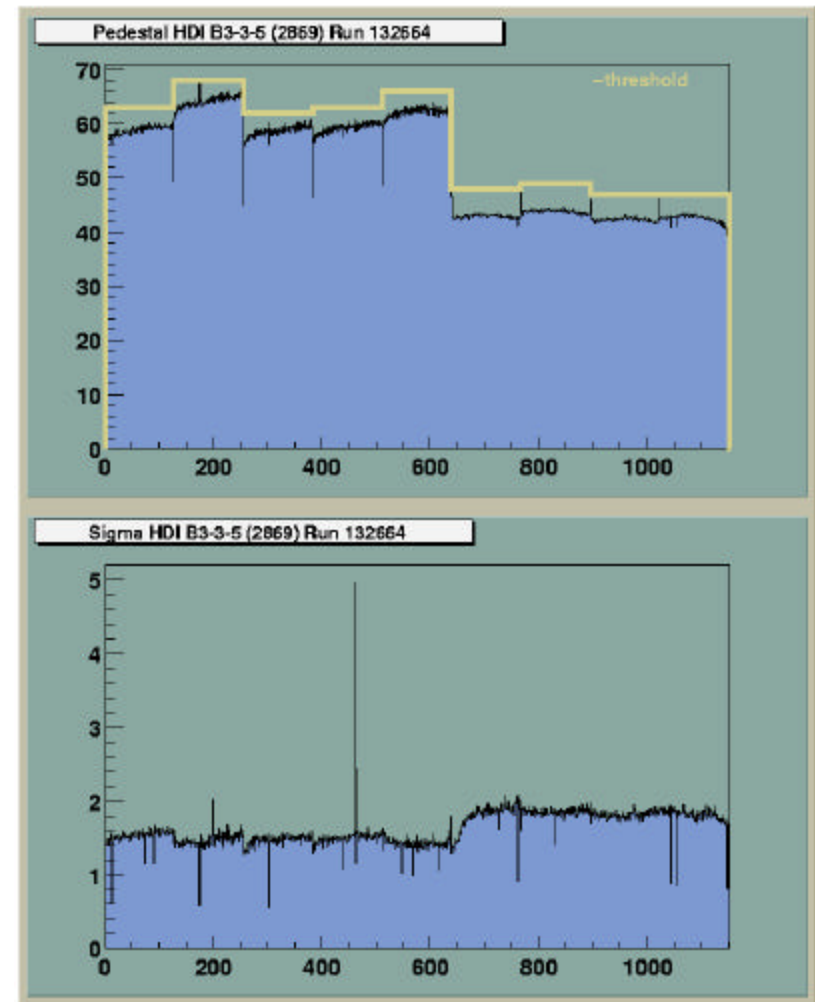
- Charge correlation between p- and n-side of a detector

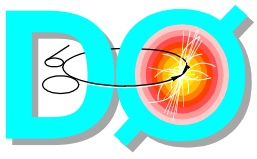




Operations: Calibrations

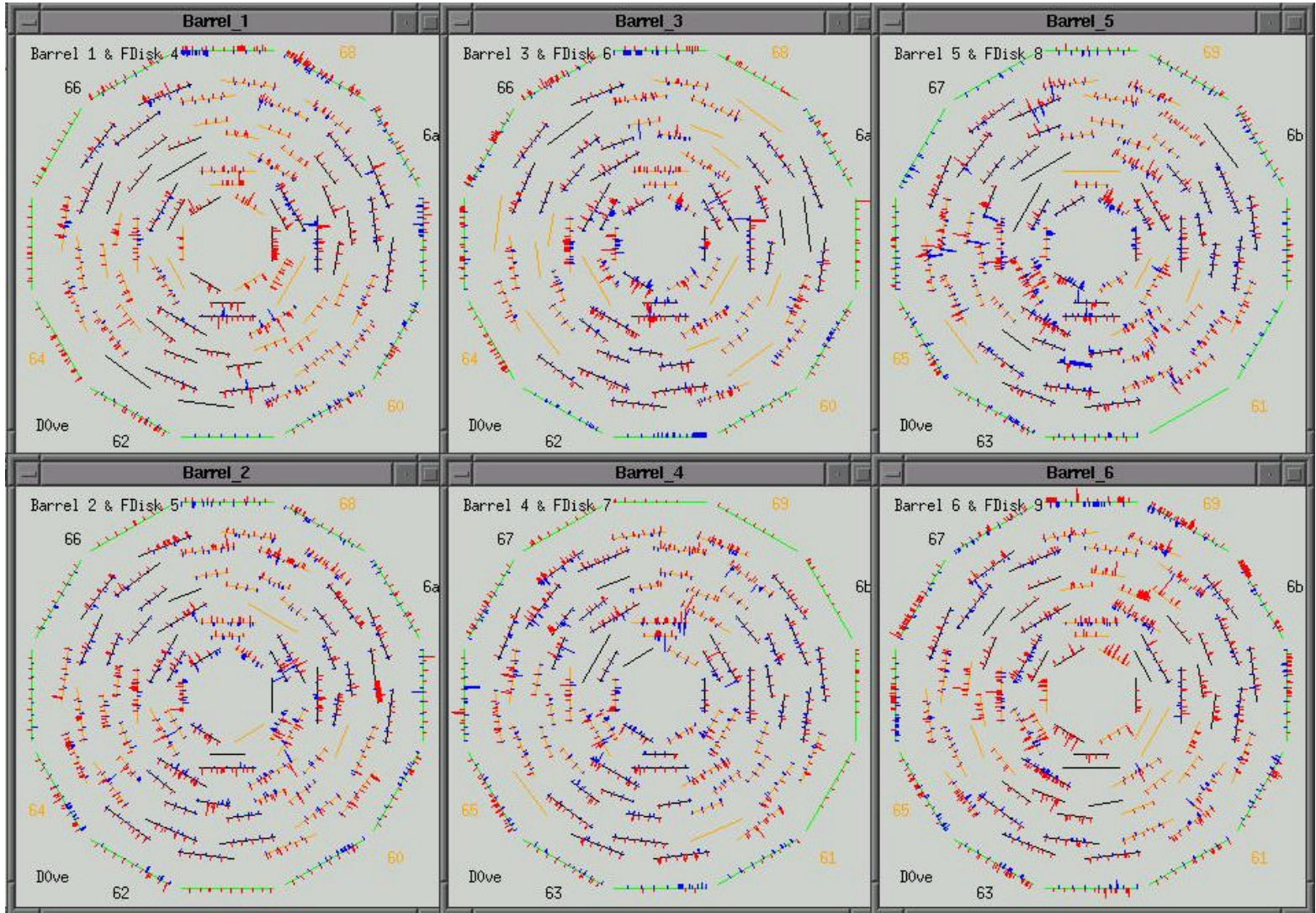
- SMT pedestal, noise and gain measurements are taken using SDAQ.
- Pedestal and noise measurements are used to calculate the threshold per chip to be used in sparse read out

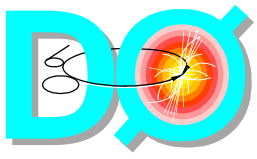




Operations issues

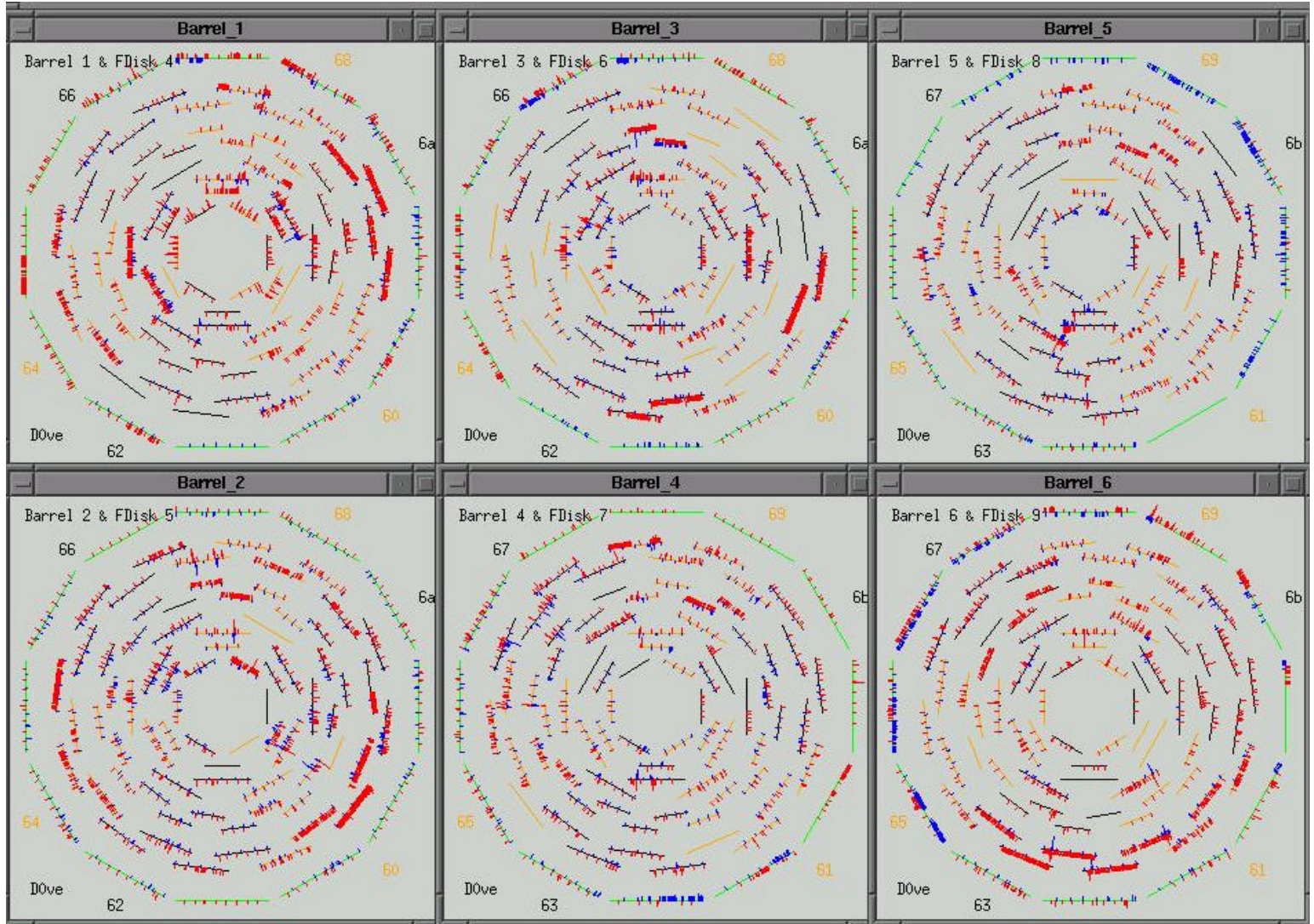
a quiet
event

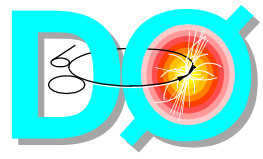




Operations issues

a busy event

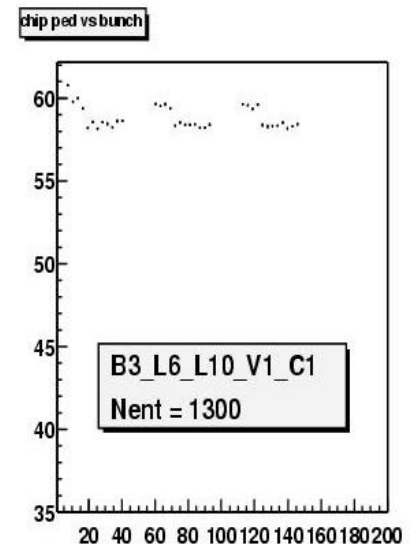
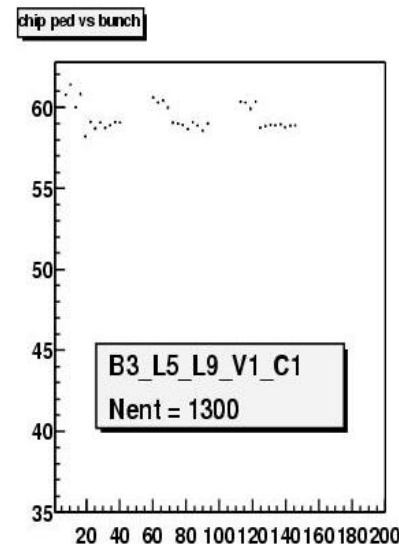
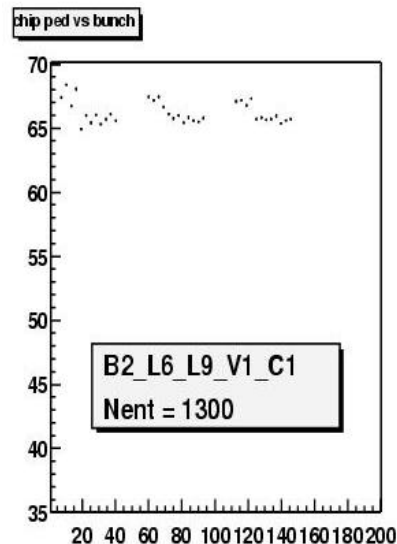
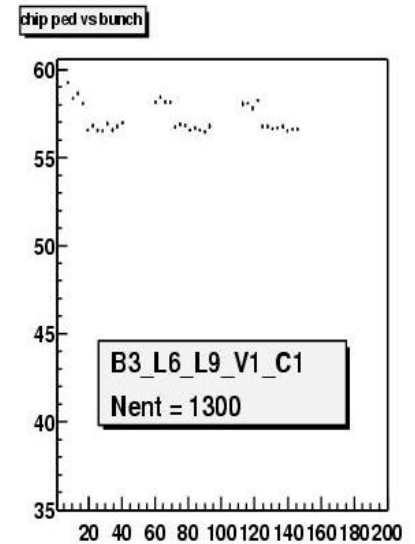
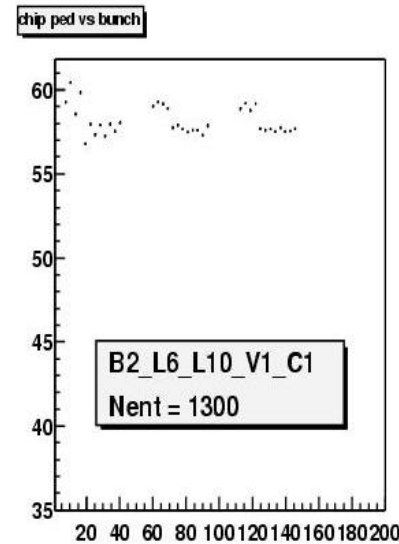
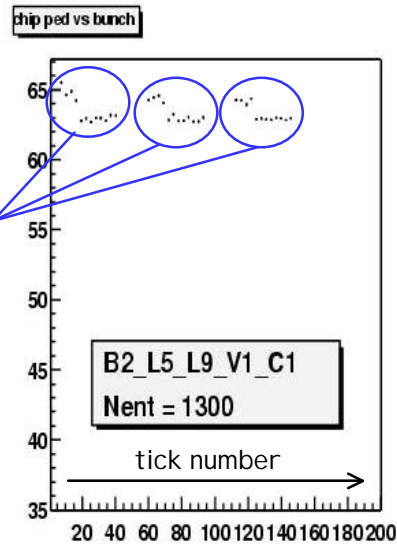


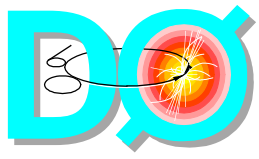


Operations issues: Pedestal shifts

3 superbunches
of 12 bunches

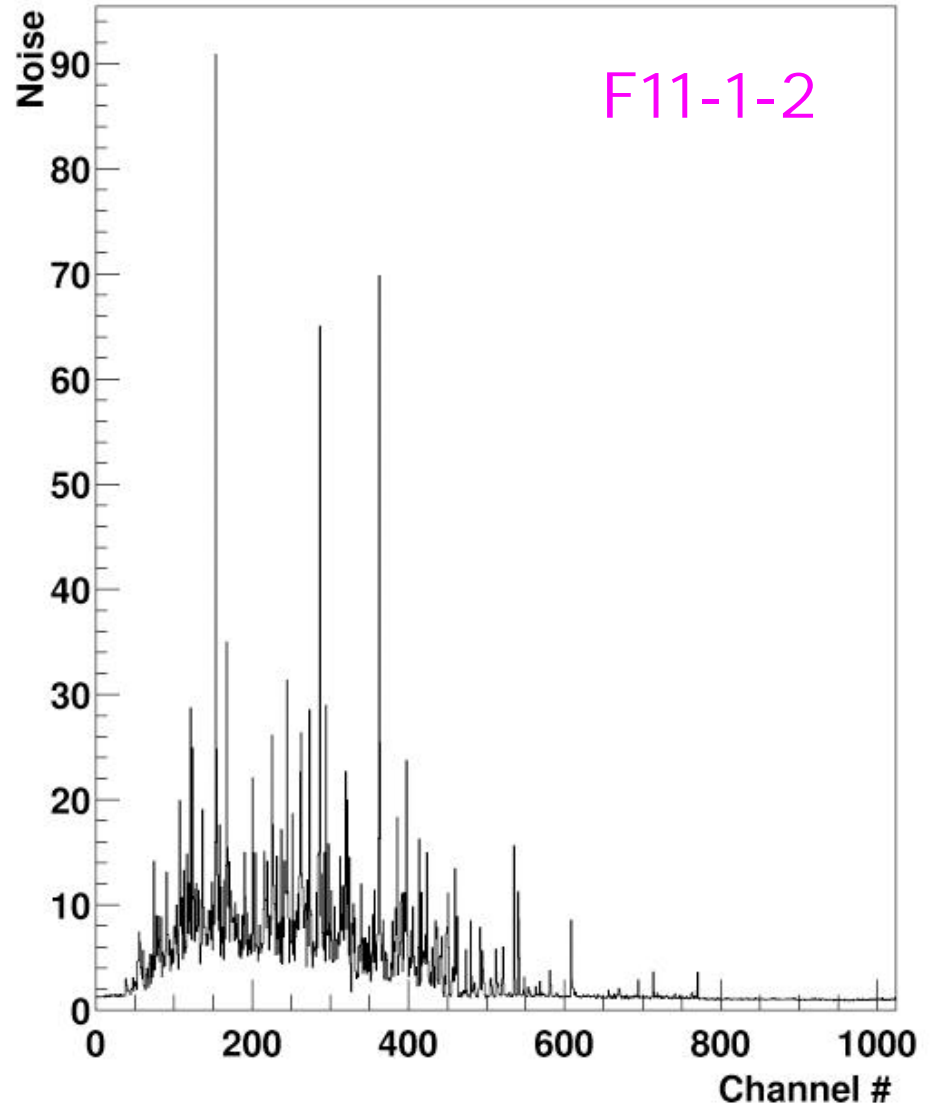
- pedestals seem to be different at the beginning of each superbunch
- Investigating ...

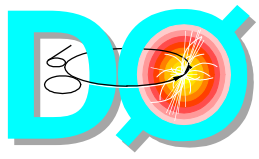




Operations issues: F-Wedges noise (1)

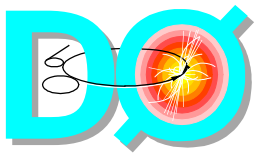
- seems to affect only the p-side of a fraction of the Micron sensors
- does not seem to depend on the biasing scheme
- does not seem to depend on temperature
- still investigating ...



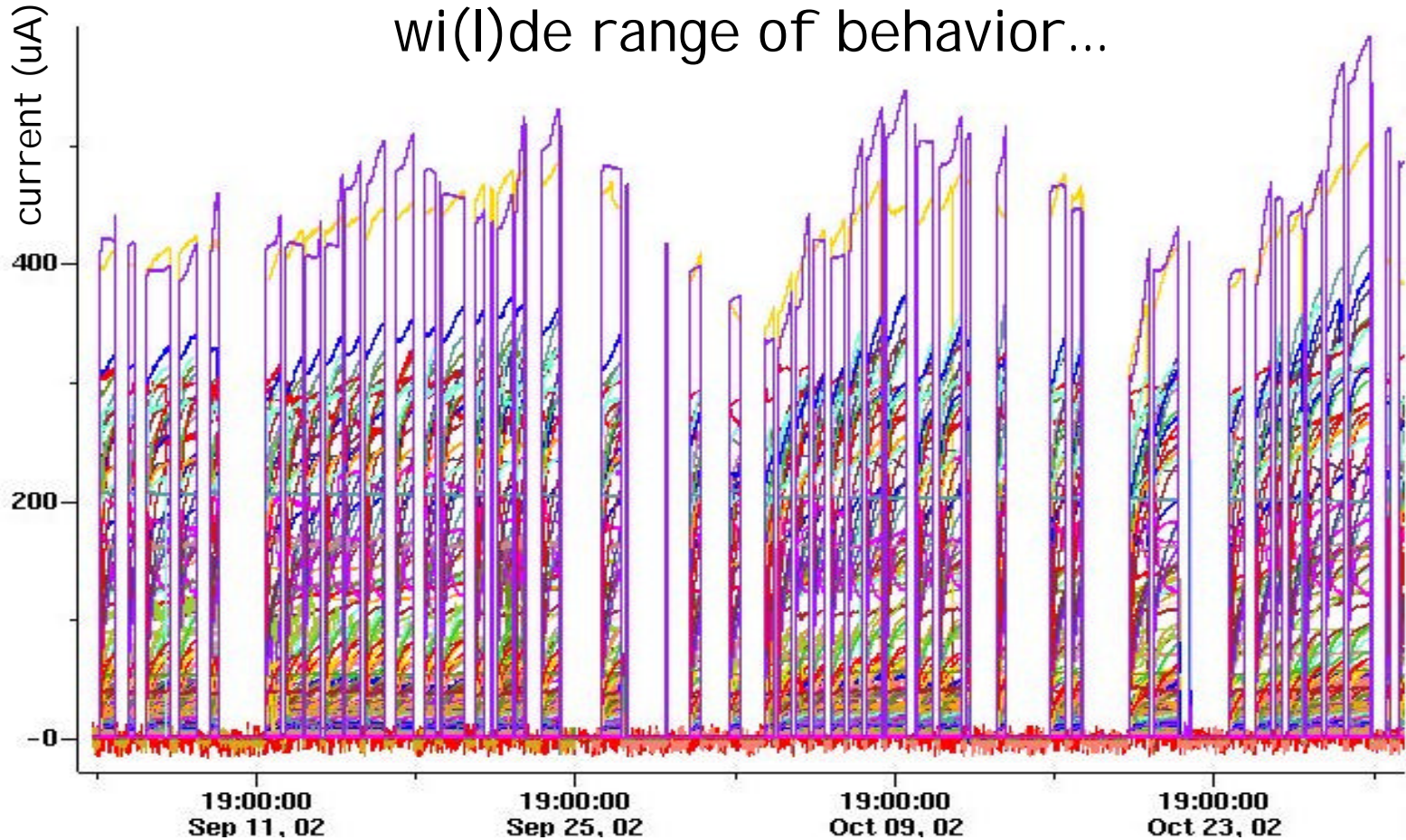


Operation issues: F-Wedges noise (2)

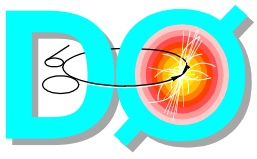
# of wedges in disk	w/ > 10% noisy strips				w/ > 20% noisy strips				w/ > 30% noisy strips			
	P-side			N-side	P-side			N-side	P-side			N-side
threshold (ADC)	4	6	10	4	4	6	10	4	4	6	10	4
01 (Micron)	6	4	1	3	2	2	1	1	1	1	0	0
02 (Micron)	4	1	0	1	2	0	0	1	1	0	0	1
03 (Eurysis)	0	0	0	0	0	0	0	0	0	0	0	0
04 (Micron)	5	4	2	2	4	3	1	1	3	2	1	1
05 (Eurysis)	0	0	0	1	0	0	0	1	0	0	0	0
06 (Micron)	7	5	5	7	6	5	3	4	4	3	2	4
07 (Micron)	3	2	2	1	2	2	1	0	1	1	0	0
08 (Eurysis)	0	0	0	0	0	0	0	0	0	0	0	0
09 (Micron)	4	4	3	2	4	3	1	1	2	2	0	1
10 (Eurysis)	0	0	0	0	0	0	0	0	0	0	0	0
11 (Micron)	5	3	3	4	3	2	0	1	2	1	0	0
12 (Micron)	6	3	2	2	2	2	2	0	2	2	0	0
TOTAL (144)	40	26	18	23	25	19	9	10	16	12	3	7



Bias currents: first look (1)

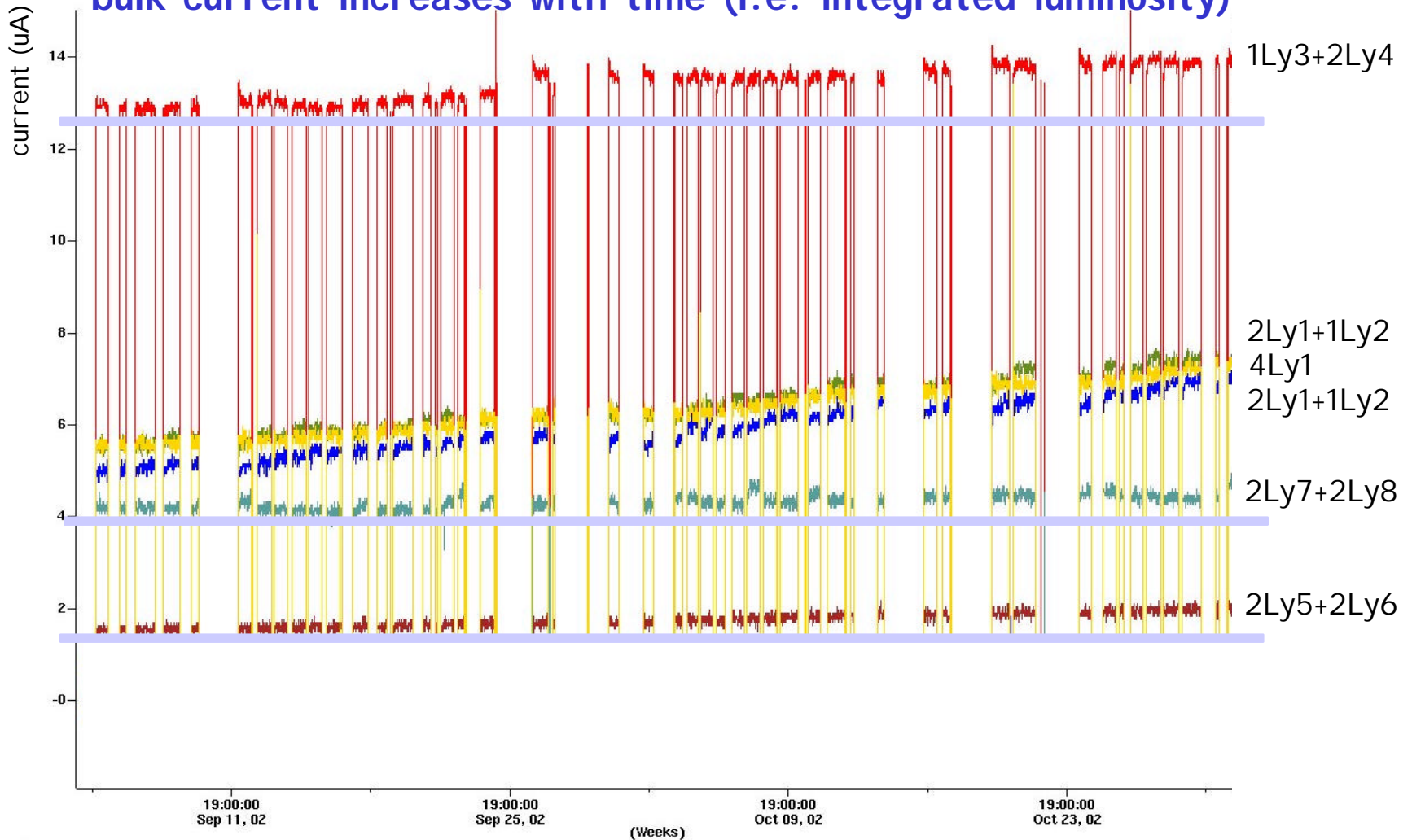


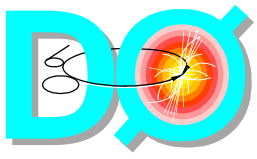
this is not bulk current.



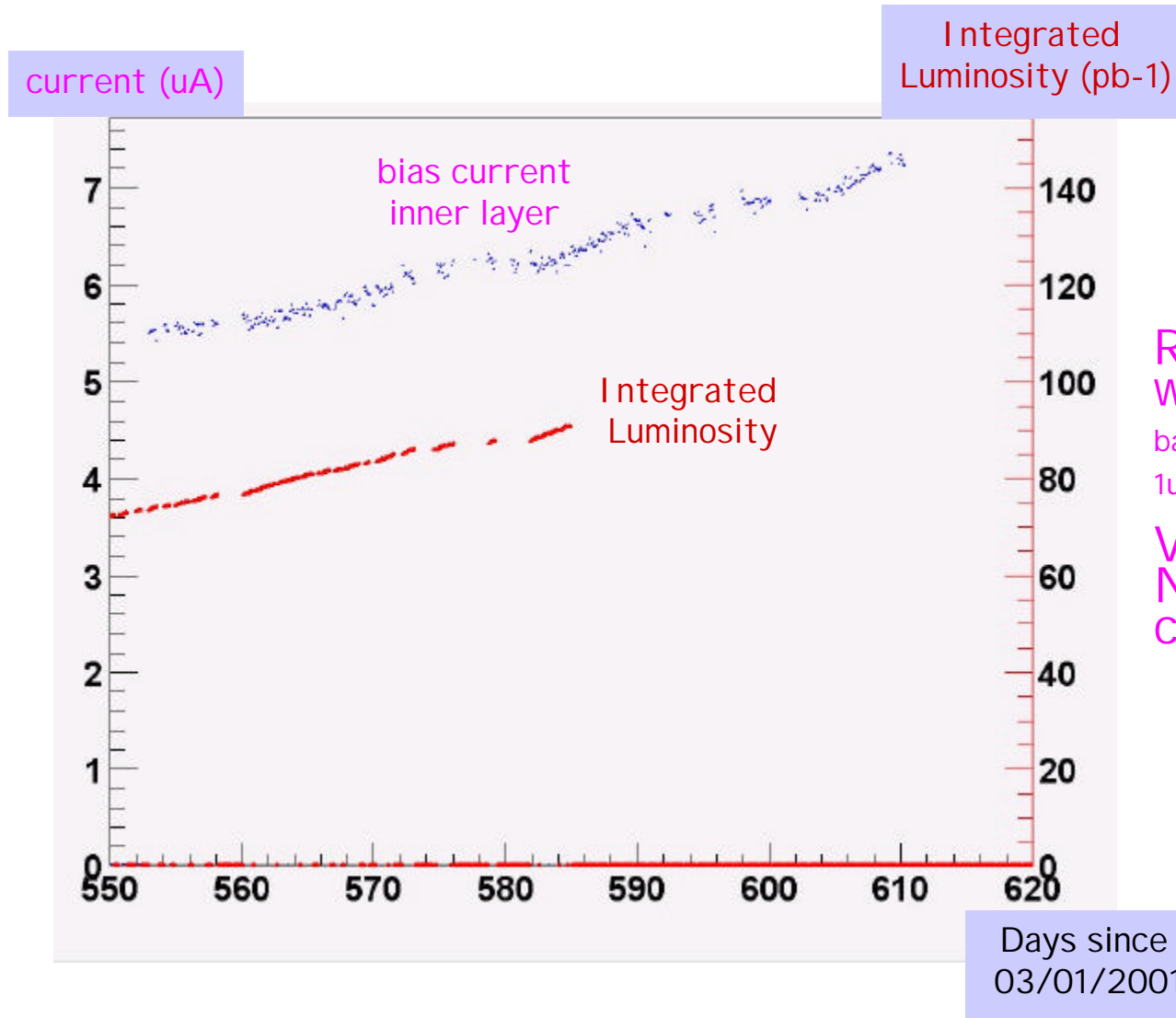
Bias currents: first look (2)

- As expected, the closer you get from the beam and the fastest the bulk current increases with time (i.e. integrated luminosity)





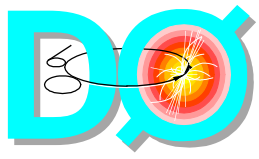
Bias currents: first look (3)



Roughly scales
with luminosity

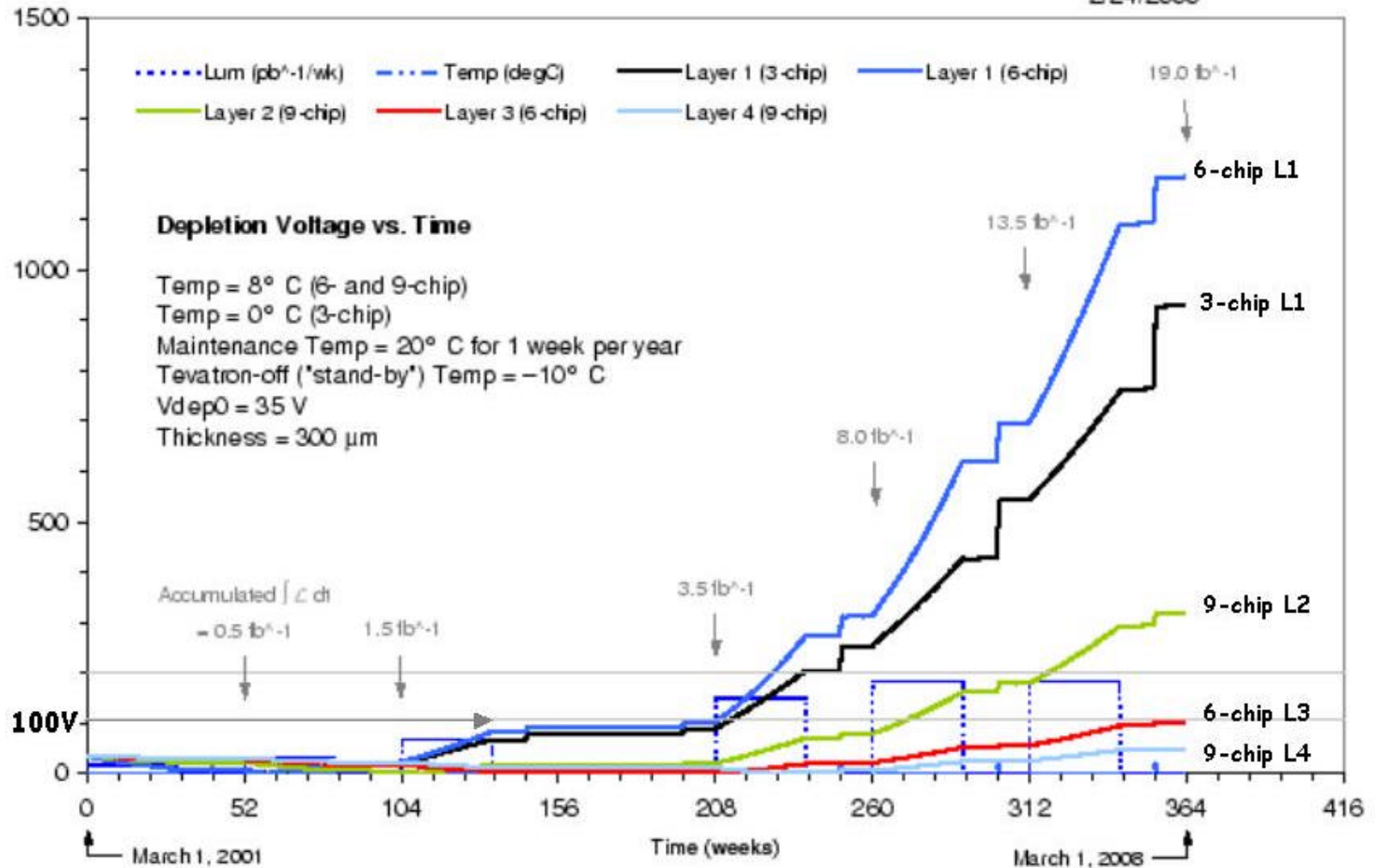
back of the envelop calculation:
 $1\mu\text{A}/20\text{pb}^{-1} \Rightarrow 100\mu\text{A}/2\text{fb}^{-1}$

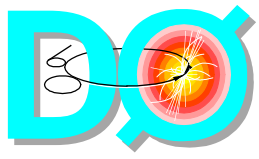
Very preliminary.
Need to have a
closer look.



Expected depletion voltage

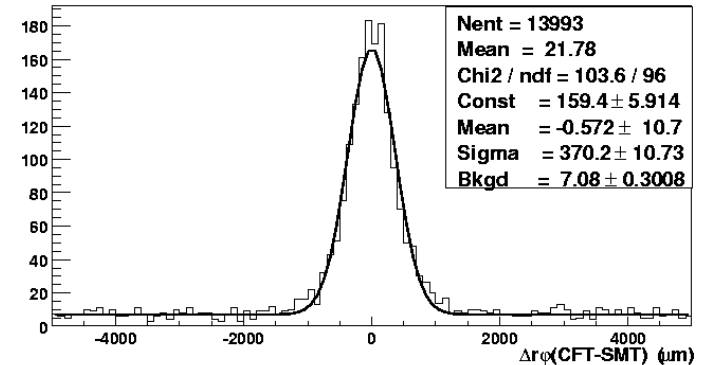
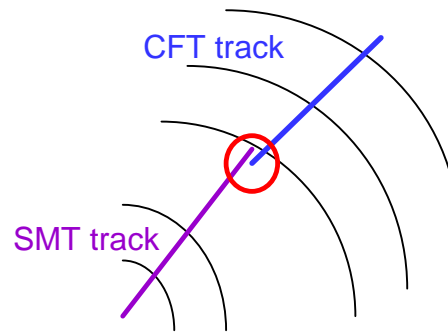
John Ellison UCR
2/24/2000



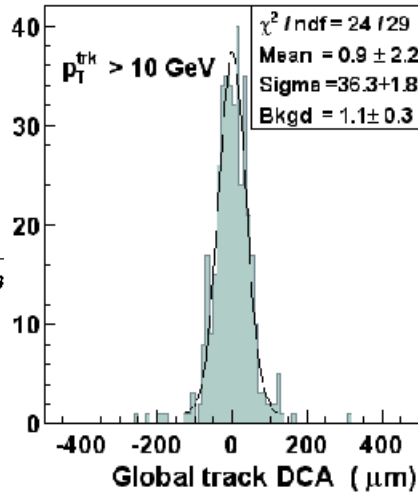
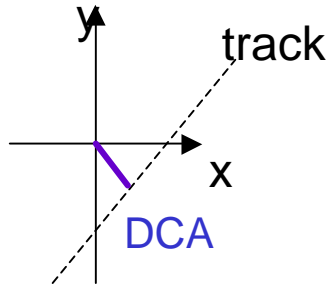


Results: Tracking and Vertexing (prelim.)

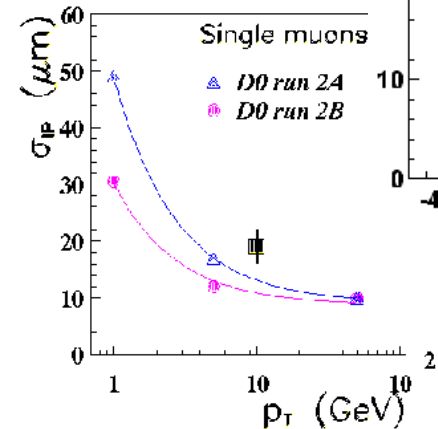
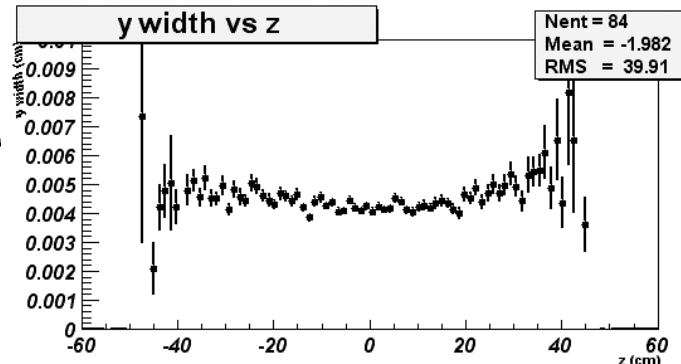
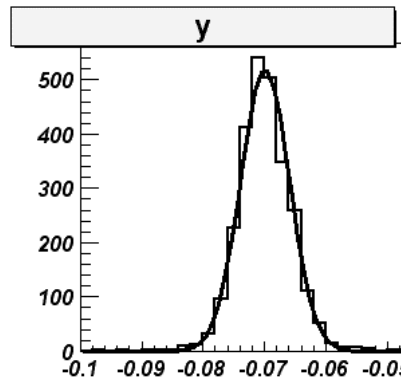
CFT-SMT track matching

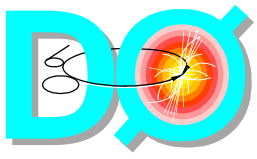


Impact parameter resolution



Vertex measurements

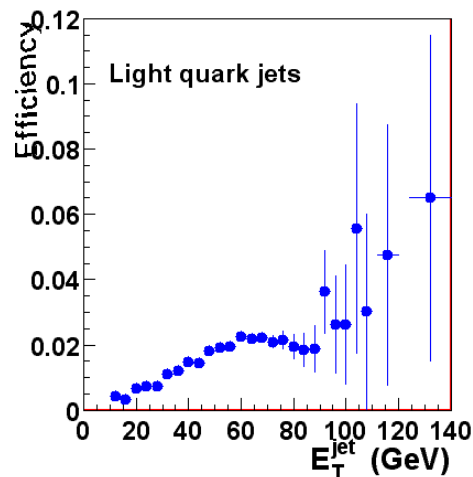
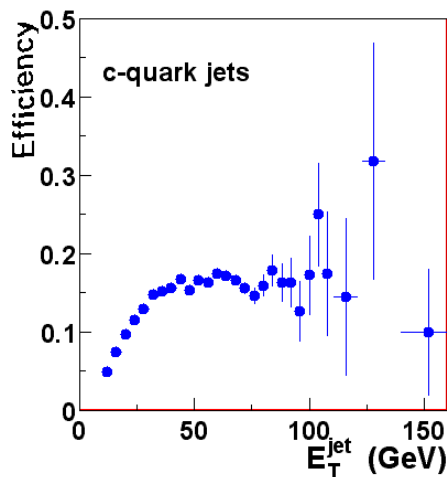
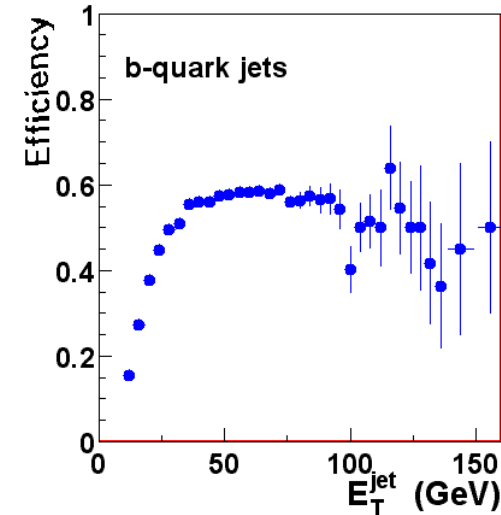
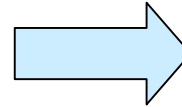




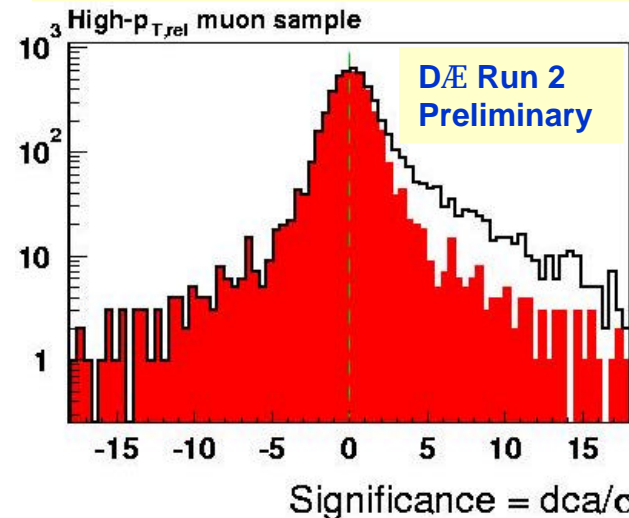
Results: b-tagging (preliminary)

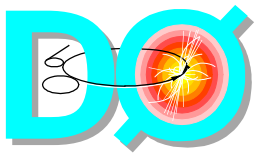
Preliminary results indicate

- b-tagging efficiency as high as 60% can be achieved
- Mis-tagging rate for c-jets is less than 15 - 20% depending on E_T , while light quark rate can be kept at a few percent level



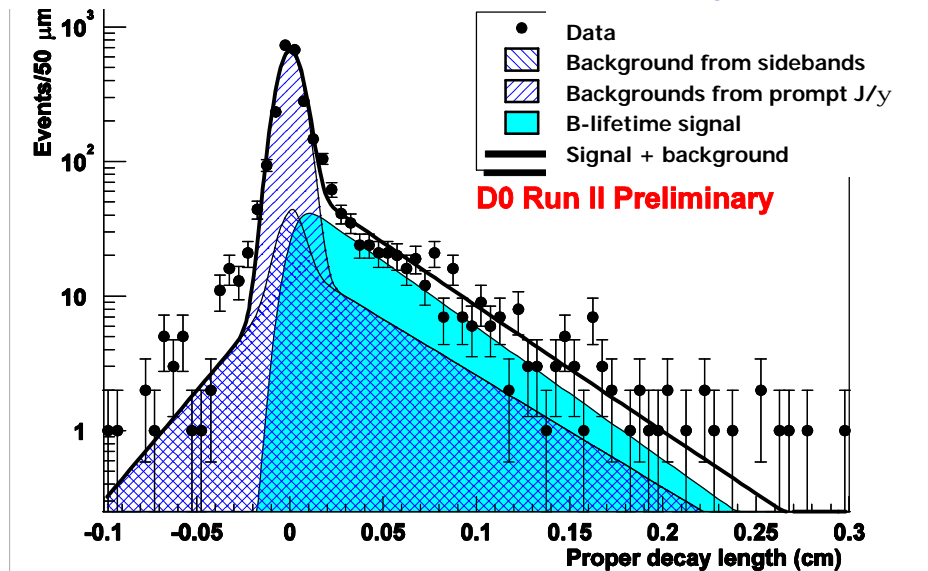
Tagging in μ +jet data sample:
muon $p_T^{\text{rel}} > 1.5$ GeV wrt the jet





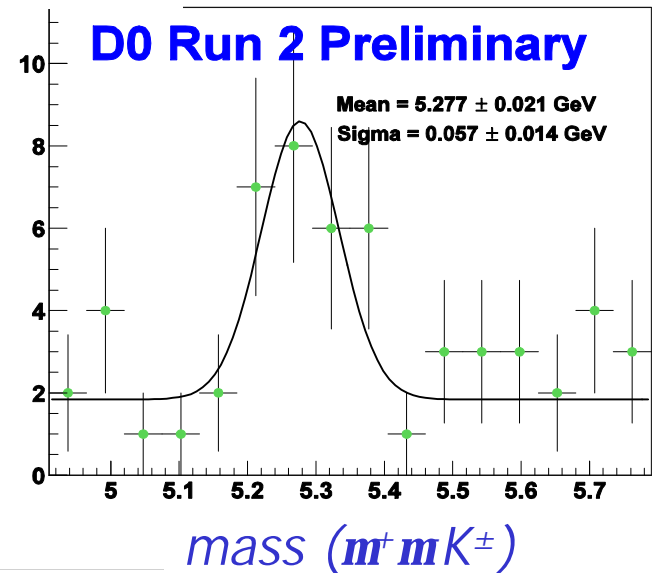
B-physics (preliminary)

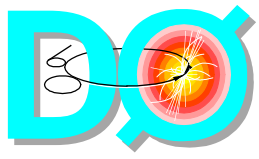
Proper B decay length ($B \rightarrow J/\psi + X$)



$B^\pm \rightarrow J/\psi K^\pm$

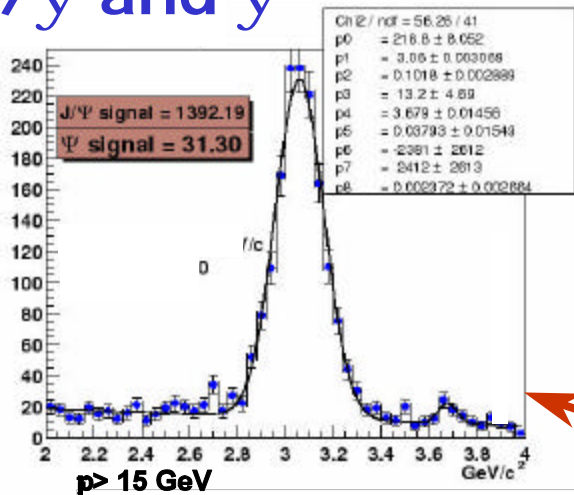
First time in DØ !



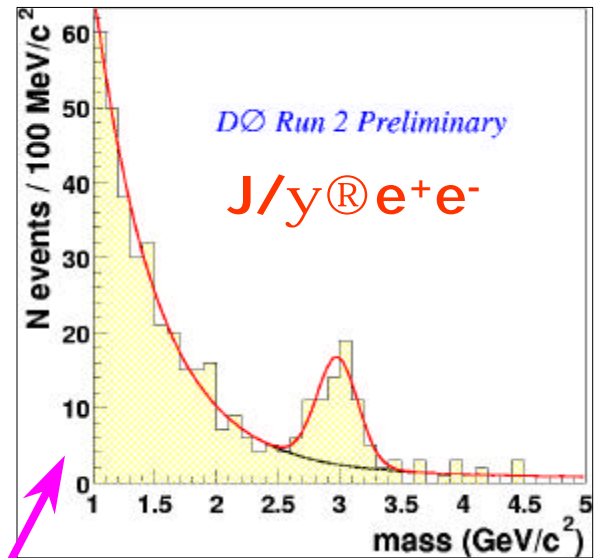


Physics with tracking (preliminary)

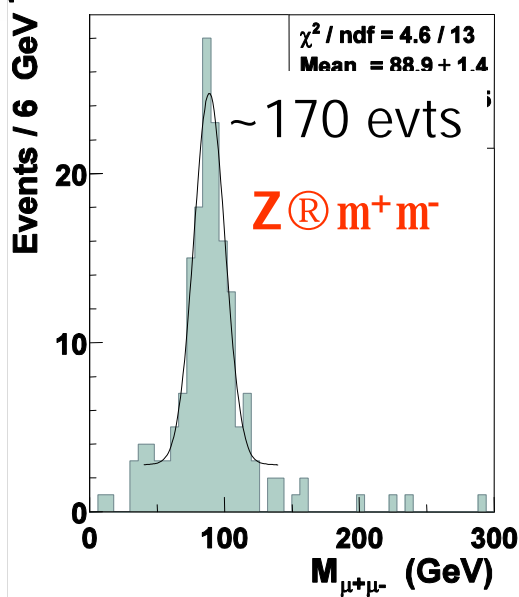
J/ψ and ψ'



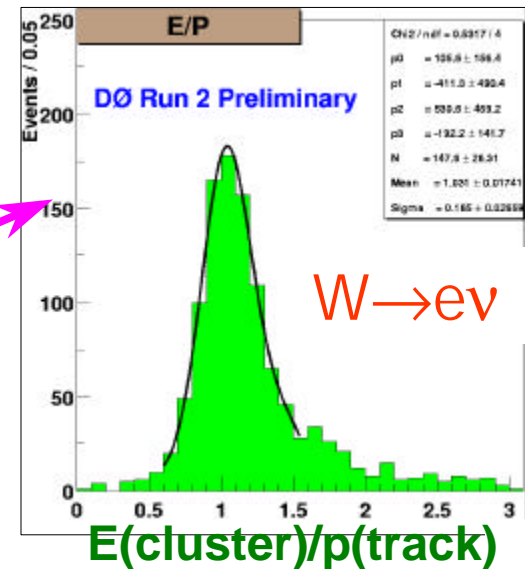
Combine tracking with other systems

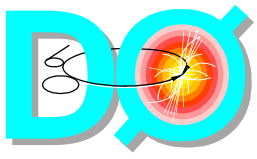


Muon System



Calorimeter





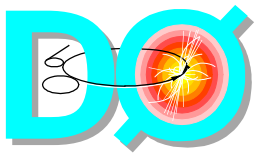
Conclusions

● Design/Production

- Experience with double-sided detectors has led to the decision to use single-sided silicon for the upgrade.
- Should work towards simpler designs in the future. For example, using 6 different sensor types resulted in extensive logistical complications.
- Had to overcome numerous vendor related problems for HDIs, Silicon Sensors, jumpers, low mass cables ...

● Assembly/Installation

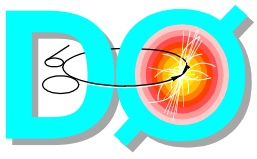
- First alignment results show that the DØ SMT was assembled and installed very well.
- The installation in the D0 detector went rather smoothly. The biggest challenge to overcome was the lack of real estate. The D0 detector, when first designed, was unfortunately not designed with a Silicon detector in mind



Conclusions

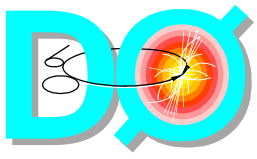
● Commissioning and operation

- The SMT was the first major DØ Upgrade detector system fully operational for Run 2a.
- We had our share of mishaps (IB PS, IB crate water leak, ...), but recovered from them.
- 90% of the channels are functional, and most of the remaining channels will be debugged and should hopefully be recovered during the January 2003 shutdown.
- Calibrations and first look at physics show that we understand our detector.
- Although the detector is close to being fully commissioned, some studies still need to be completed.



Partial to-do list

- Some studies to complete:
 - Pedestal shifts
 - where does it come from
 - how to suppress it
 - F-wedge excess noise:
 - where does it come from
 - how to suppress it
 - Bias currents:
 - study the effect of radiation
 - Effect of magnetic field on wire bonds
- Go to the next level of sophistication:
 - Online:
 - develop more monitoring tools
 - Offline:
 - alignment
 - clustering
 - tracking (efficiency, fully implement disks ...)
 - simulation



Conclusions

● General

- Construction and commissioning of the SMT has been an adventure full of challenges. But thanks to the relentless efforts of many physicists, engineers and technicians, DØ has now a vertex detector to do physics with. Results start pouring ...
- We had so much fun building this detector for run 2a that we are planning to build a completely new Silicon Microstrip detector for run 2b (see Kazu's talk)